EP-R&D Silicon Working Group 1.1

Hybrid Detectors

Small pitch 3D Timing (& planar ☺)

Evangelos –Leonidas Gkougkousis

CERN EP-R&D

Lecce – June 22nd, 2022

•Introduction, EP-R&D W.P. 1.1 – Hybrid Sensors

Planar Sensors (J. Haimberger, V. Gkougkousis)

- ✓ Radiation damage and trapping model validation though TCAD
- ✓ Timing and efficiency at < 1e17 n_{eq}/cm^2 using fast neutrons and ps protons (thicknesses 50, 100, 200, 300 μm)

LGADs (V. Gkougkousis)

- ✓ Radiation damage mechanisms and modeling on different dopant types (TIPP2021, ArXiV Preprint, PicoSecond Workshop 2021)
- ✓ Indium-Lithium gain layer radiation hardness investigations (Trento2021)
- ✓ Process simulations and SiMS – Carbon/Boron (LINK)

Silicon Electron Multiplier (M. Halvorsen, LINK, ArXiV Preprint, IEEE)

- ✓ Structure optimization and electrostatic simulations
- ✓ Timing and transient Simulations
- ✓ Process iterations (Metal Assisted Etching)

Talks @ Trento 2022

Small Pitch 3Ds for tacking and timing (V. Gkougkousis, LINK)

- ✓ β particles timing studies on irradiated and unirradiated devices
- ✓ Test beam with SPS pions (Tracking + Timing)
- ✓ Proton and neutron irradiations > 1e17 n_{eq}/cm^2
- ✓ New small pitch production optimized for gain at electrode region

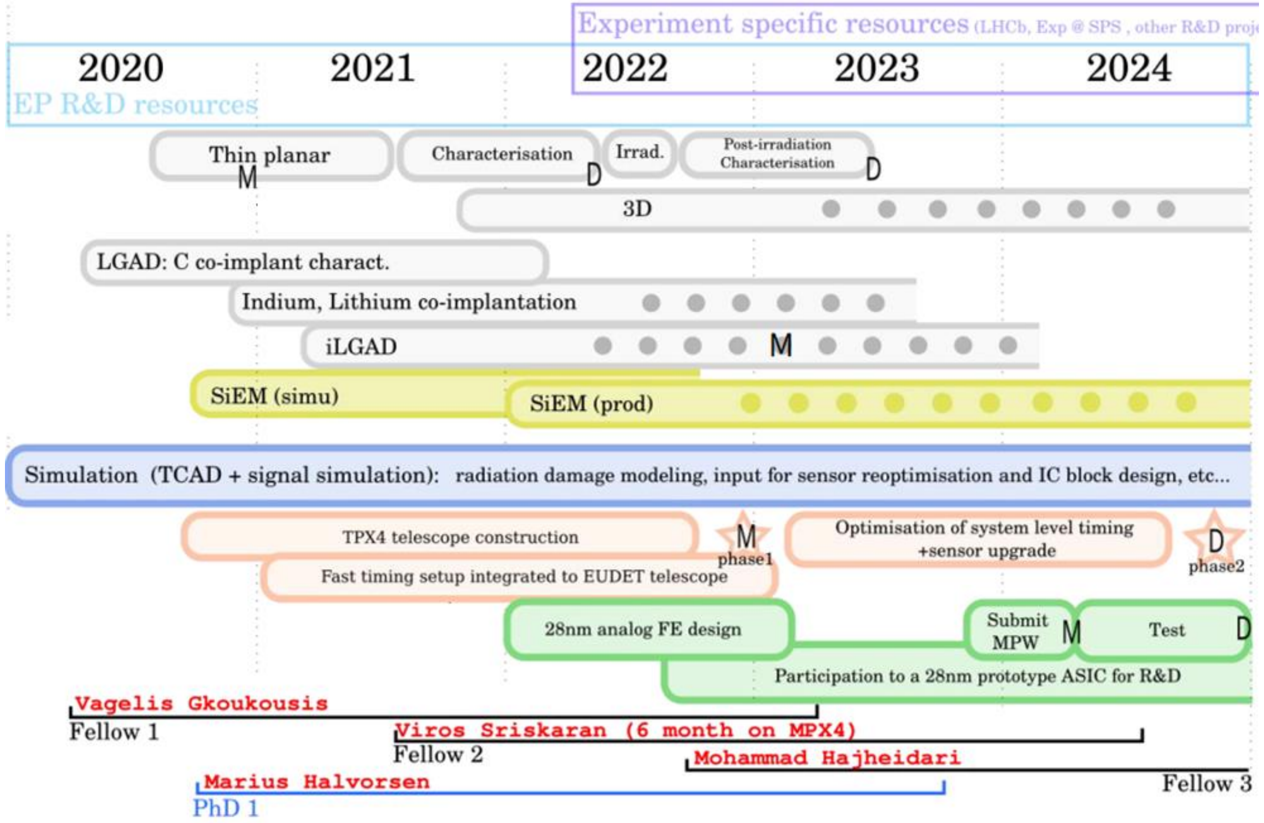

Vagelis Gkougkousis


Jakob Haimberger


Marius Halvorsen


Victor Coco


Paula Cliins


Experiment specific resources (LHCb, Exp @ SPS , other R&D proj

2020 2021 2022 2023 2024

EP R&D resources

Thin planar M

Characterisation D

Irrad.

Post-irradiation Characterisation D

3D

LGAD: C co-implant charact.

Indium, Lithium co-implantation

iLGAD M

SiEM (simu)

SiEM (prod)

Simulation (TCAD + signal simulation): radiation damage modeling, input for sensor reoptimisation and IC block design, etc...

TPX4 telescope construction

M phase1

Fast timing setup integrated to EUDET telescope

Optimisation of system level timing +sensor upgrade

D phase2

28nm analog FE design

Submit MPW M

Test D

Participation to a 28nm prototype ASIC for R&D

Vagelis Gkoukousis

Fellow 1

Viros Sriskaran (6 month on MPX4)

Fellow 2

Mohammad Hajheidari

Fellow 3

Marius Halvorsen

PhD 1

•3D Sensors

Timing at Extreme Fluences

3D Sensors: Decoupling of charge generation and drift volume
(*Standard columns, TimeSpot, Hex geometries* ect.)

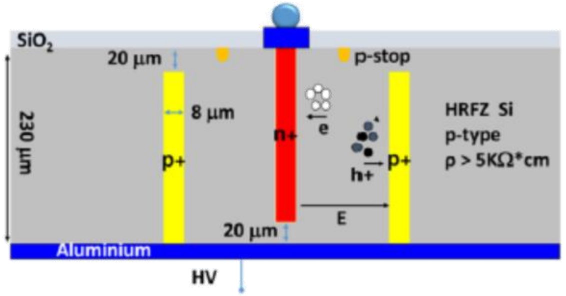
Pros

- High radiation tolerance up to several times 10^{16} n_{eq}/cm^2
- Short drift distances with fast rise times
- Reduced Landau fluctuation, practically non-existent for perpendicular tracks

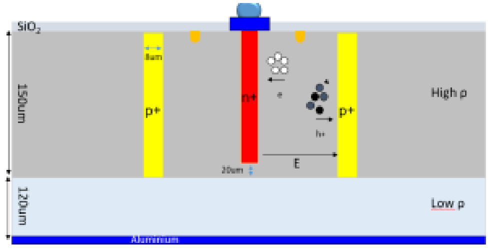
Cons

- Non-uniform field geometry
- High cost
- Increased cell capacitance

Double Sided
(thicker, more expensive)

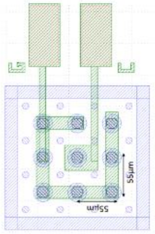


Single Sided
(thinner, simpler process)



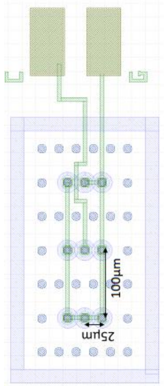
Pixel Size vs Field Uniformity

ATLAS IBL Type

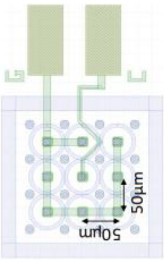


- ✓ Double sided n-on-p process
- ✓ Pixel Size 55 × 55 µm²
- ✓ Active thickness 230 µm
- ✓ High Resistivity (> 2 kΩm × cm) Fz silicon

ATLeS Pre-Production type



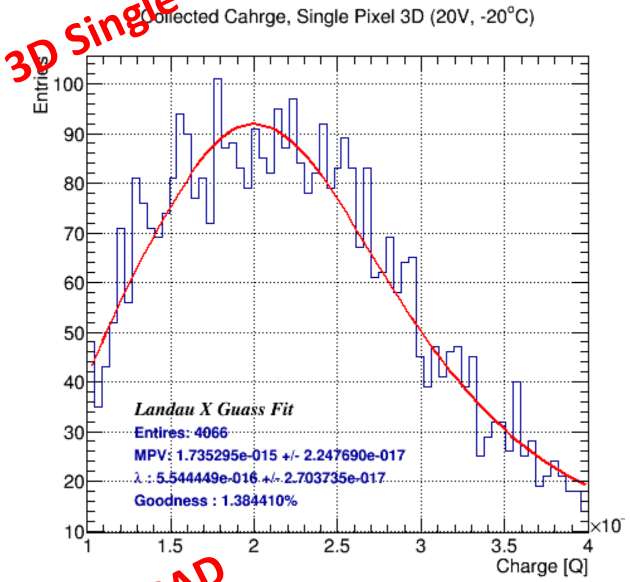
- ✓ Single sided n-on-p process
- ✓ Pixel Size 25 × 100 µm²
- ✓ Active thickness 150 µm
- ✓ High Resistivity (> 2 kΩm × cm) Fz silicon

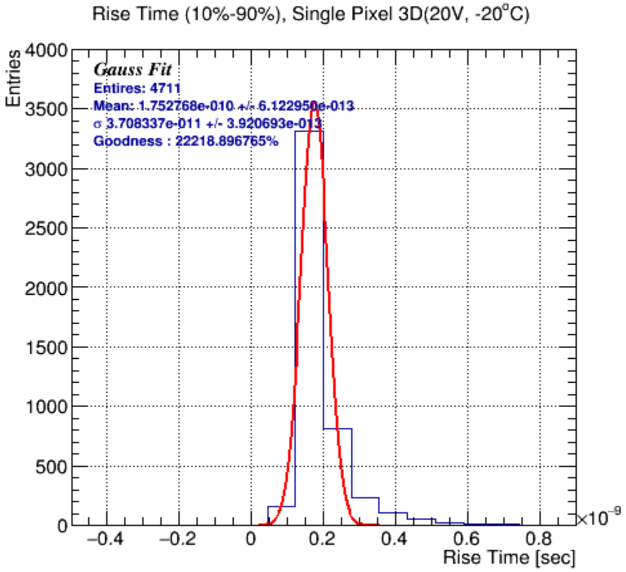


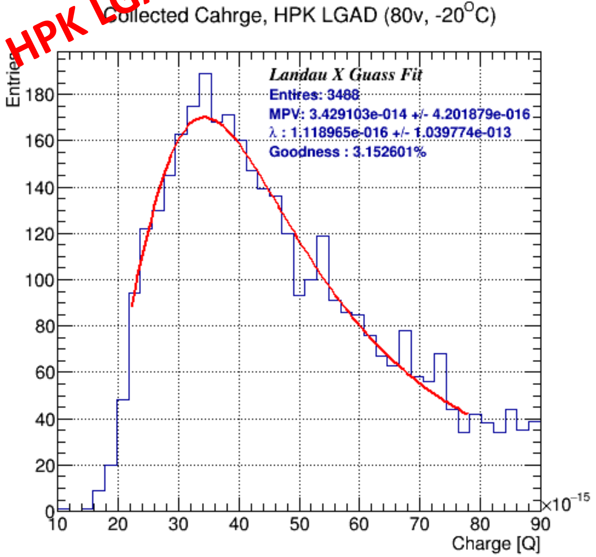
- ✓ Single sided n-on-p process
- ✓ Pixel Size 50 × 50 µm²
- ✓ Active thickness 150 µm
- ✓ High Resistivity (> 2 kΩm × cm) Fz silicon

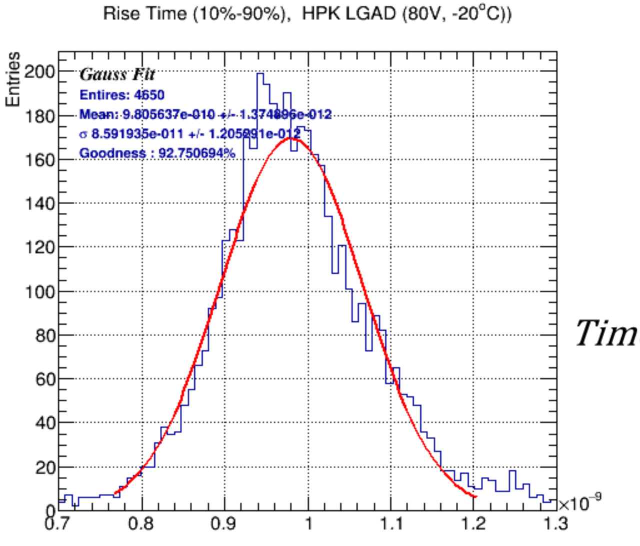
•3D Sensors - Timing

Presentation: V. Gkougkousis, "Single cell 3D timing: Time resolution assessment and Landau contribution evaluation via test-beam and laboratory measurements", 17th Trento workshop on advanced radiation silicon detectors (link)





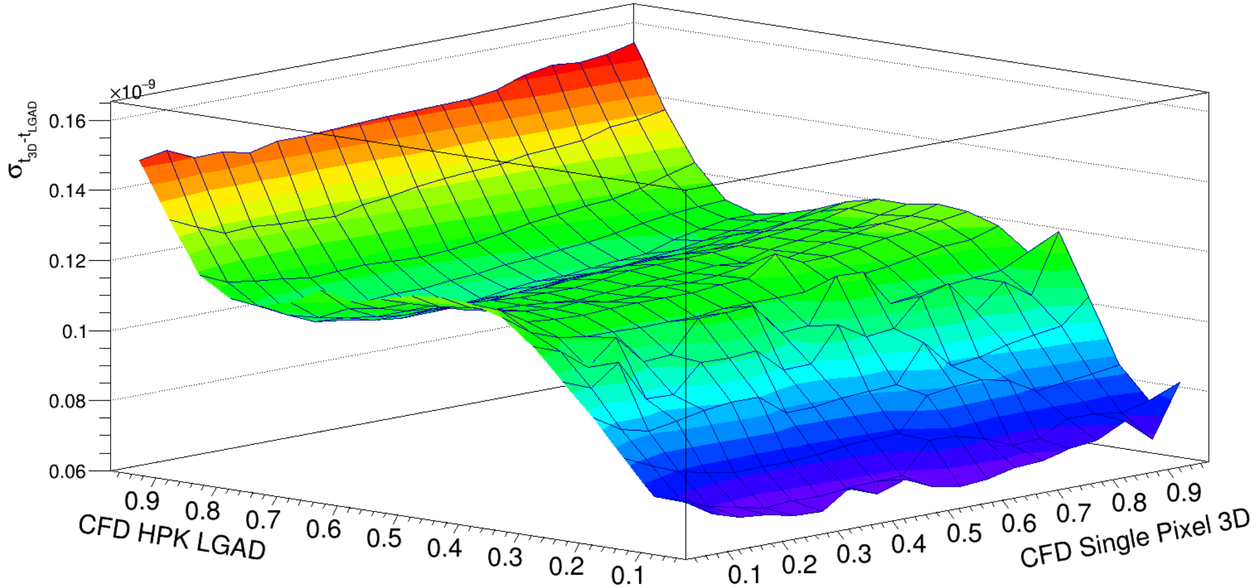




- **Extremely fast rising edge (< 180 psec)**
- **Linear stable behavior with CFD, good SNR control**

$$(\sigma_{\mathrm{Dut}})_{CFD_{ij}} = \sqrt{(\sigma^2_{\mathrm{Tot}})_{CFD_{ij}} - (\sigma^2_{\mathrm{Ref}})_{CFD_i}}$$

CFD Map, LGAD - Single Pixel 3D (-20°C, 20V)



2D optimization plot – 0.5% binning

Time Resolution: $\sigma^2_{tot} = \underbrace{\sigma^2_{timewalk}}_{\sigma^2_{Dist.} + \sigma^2_{Landau}} + \underbrace{\sigma^2_{jitter}}_{\left(\frac{t_{rise}}{S/N}\right)^2} + \underbrace{\sigma^2_{conversion}}_{\left(\frac{TDC_{bin}}{\sqrt{12}}\right)^2} + \underbrace{\sigma^2_{Clock}}_{\text{Fixed Term} \sim 5\text{-}7\ psec}$

•Planar Sensors

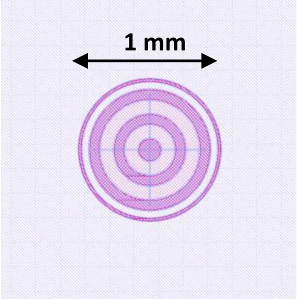
Sensors: CERN EP-R&D n-on-p planar sensor run with ADVACAM at 50, 100, 200 and 300 μm active thickness (TimePix4 bonded sensors also from this run, see Kazu's talk here)

Test Structures

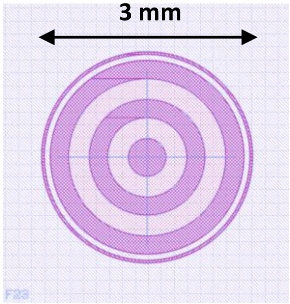
- Small diodes (3.14 mm2 active area) Circular diodes for timing studies due to lower capacitance
- Big diodes (28.27 mm2 active area) Circular diodes for radiation damage studies
- 5x5 Pixel matrix (0.003 mm2 active area) for charge sharing and interpixel efficiency – timing studies

Issues

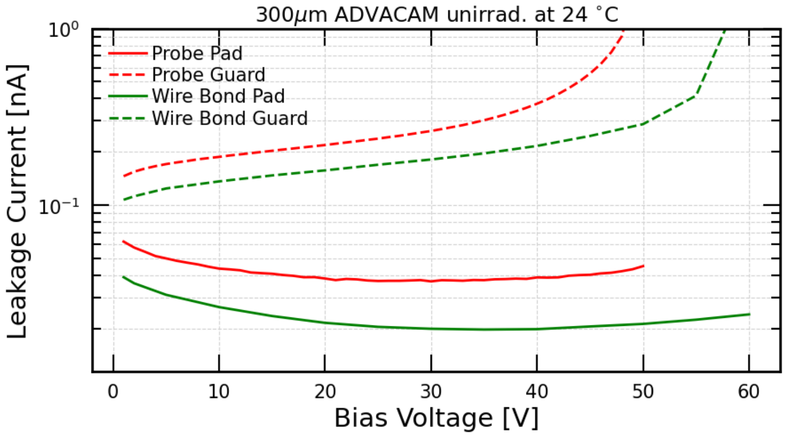
- Early breakdown due to high p-spray concentration leading to impact ionisation at the interface between p-spray and electrode implant
- Breakdown first visible in guard ring due to bigger interface region compared to pad

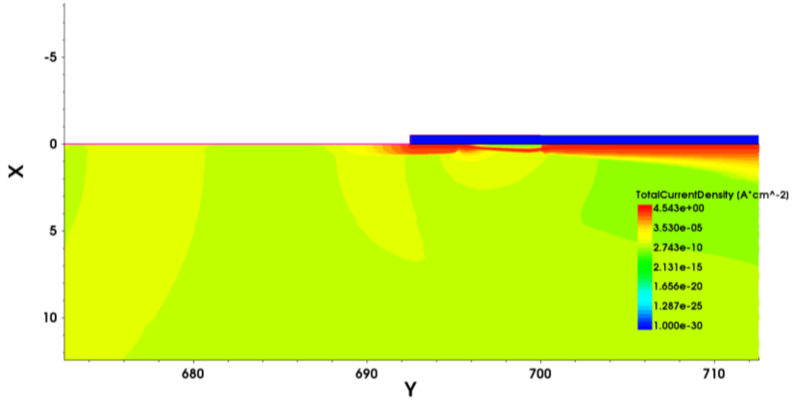


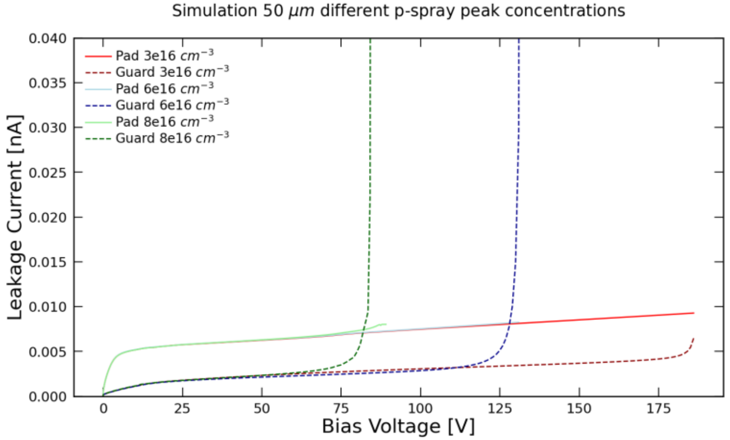
Small Diode



Big Diode







Irradiations

(both 3D and planar)

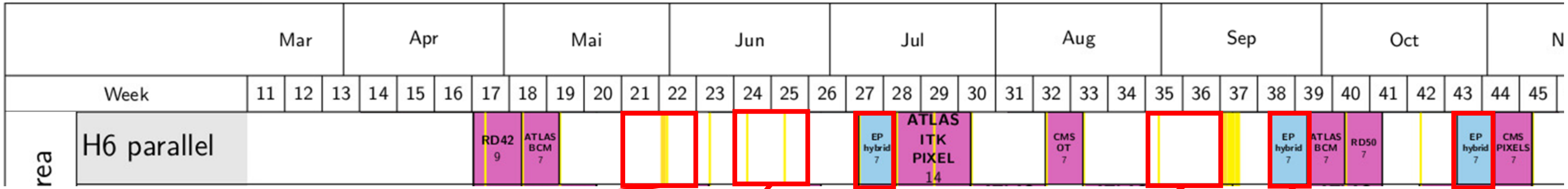
Neutron @ JSI (Ljubljana)

- ✓ $1 \times 10^{15}\ n_{eq}/cm^2$
- ✓ $8 \times 10^{15}\ n_{eq}/cm^2$
- ✓ $6 \times 10^{16}\ n_{eq}/cm^2$
- ✓ $1 \times 10^{17}\ n_{eq}/cm^2$

Proton @ PS

- ✓ $1 \times 10^{15}\ n_{eq}/cm^2$
- ✓ $8 \times 10^{15}\ n_{eq}/cm^2$
- ✓ $6 \times 10^{16}\ n_{eq}/cm^2$
- ✓ $1 \times 10^{17}\ n_{eq}/cm^2$

•Test Beam Planning



rea		Mar			Apr				Mai				Jun				Jul				Aug				Sep				Oct				N
	Week	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45
	H6 parallel							RD42 9	ATLAS BCM 7									EP hybrid 7	ATLAS ITK PIXEL 14				CMS OT 7						EP hybrid 7	ATLAS BCM 7	RD50 7			EP hybrid 7	CMS PIXELS 7	

Primary user
Parallel user
Parasitic user

25 May – 8 June

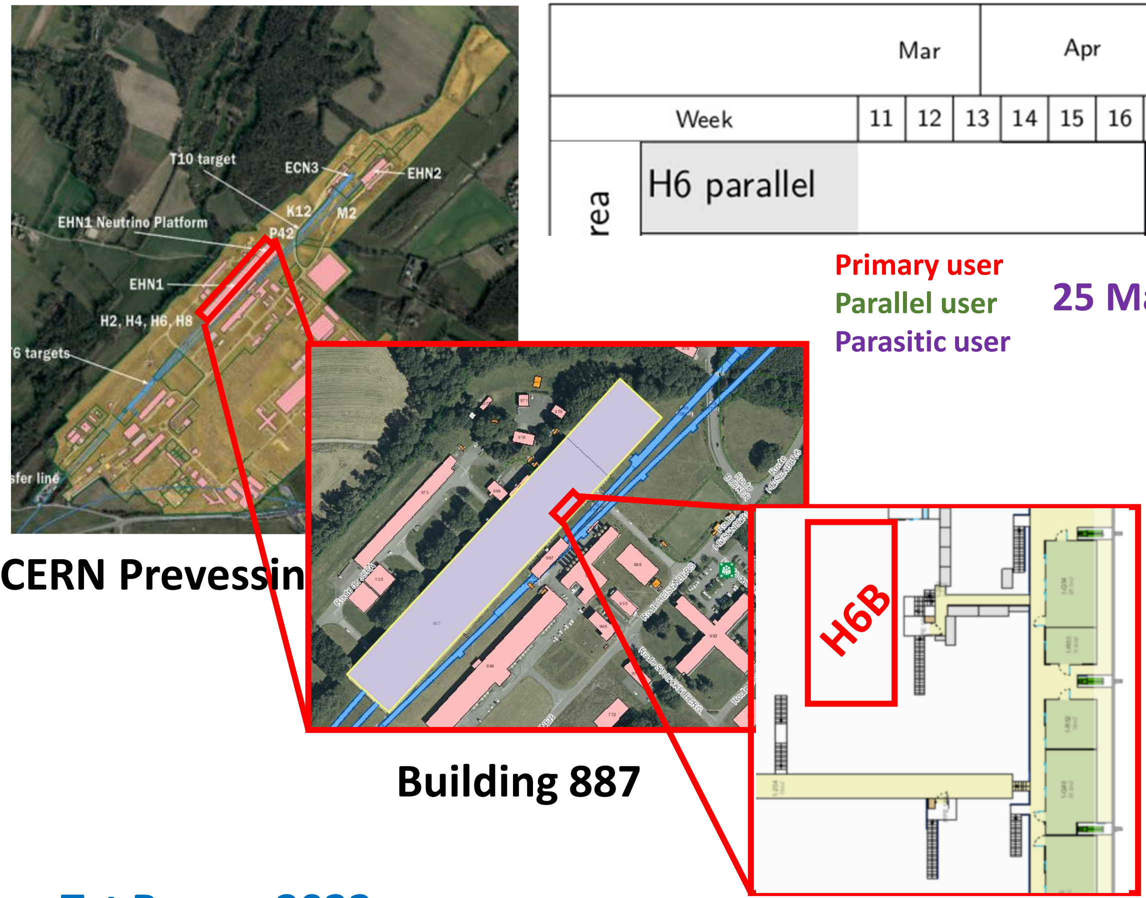
15 – 29 June

6 July – 13 July

31 August - 14 September

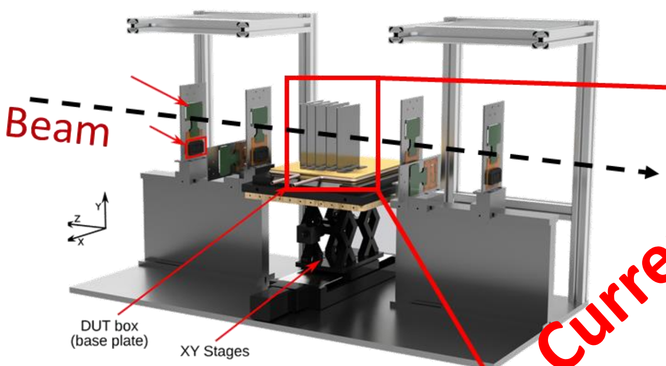
20 - 27 September

17 – 24 October

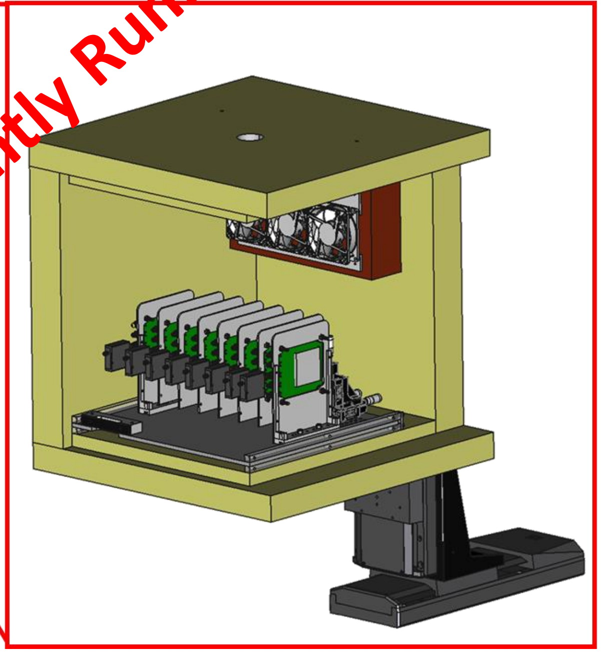


CERN Prevessin

Building 887



Currently Running!!



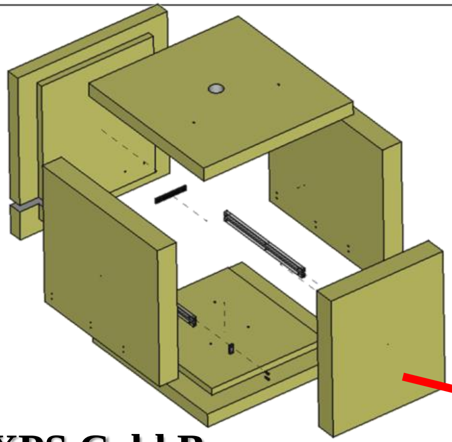
Tet Beams 2022

- Several periods but only two as primary user
- Main target irradiated Planar / 3D sensors
- No / Limited possibility of extension
- Extensive infrastructure developments

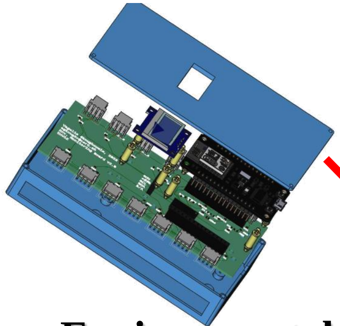
The Setup

- AIDA Telescope
- Custom Cold Box
- DUTs on individual stages
- Discrete electronics and Oscilloscope

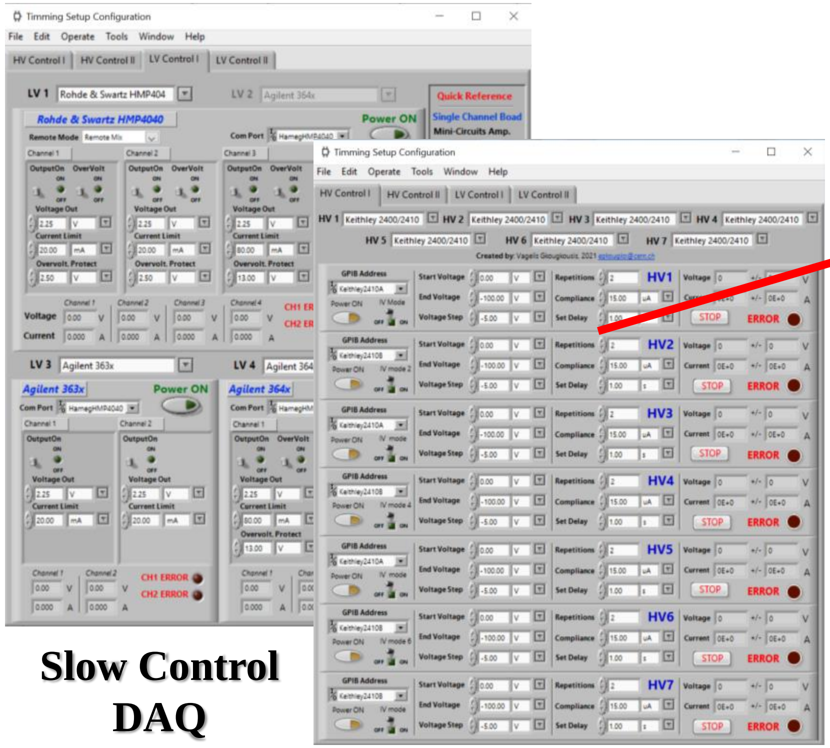
•Setup @ SPS



XPS Cold Box



Environmental Control



Timming Setup Configuration — LV Control I

LV 1 Rohde & Swartz HMP404

LV 2 Agilent 364x

Rohde & Swartz HMP4040

Remote Mode Remote Mix

Com Port HamegHMP4040

Channel 1: Voltage Out 2.25 V; Current Limit 20.00 mA; Overvolt. Protect 2.50 V

Channel 2: Voltage Out 2.25 V; Current Limit 20.00 mA; Overvolt. Protect 2.50 V

Channel 3: Voltage Out 2.25 V; Current Limit 80.00 mA; Overvolt. Protect 13.00 V

Voltage: Channel 1 0.00 V; Channel 2 0.00 V; Channel 3 0.00 V; Channel 4 0.00 V

Current: Channel 1 0.000 A; Channel 2 0.000 A; Channel 3 0.000 A; Channel 4 0.000 A

LV 3 Agilent 363x

LV 4 Agilent 364x

Agilent 363x — Com Port HamegHMP4040

Channel 1: Voltage Out 2.25 V; Current Limit 20.00 mA

Channel 2: Voltage Out 2.25 V; Current Limit 20.00 mA

Channel 1: 0.00 V; 0.000 A

Channel 2: 0.00 V; 0.000 A

Agilent 364x — Com Port HamegHM

Channel 1: Voltage Out 2.25 V; Current Limit 80.00 mA; Overvolt. Protect 13.00 V

Channel 1: 0.00 V; 0.000 A

Timming Setup Configuration — HV Control I

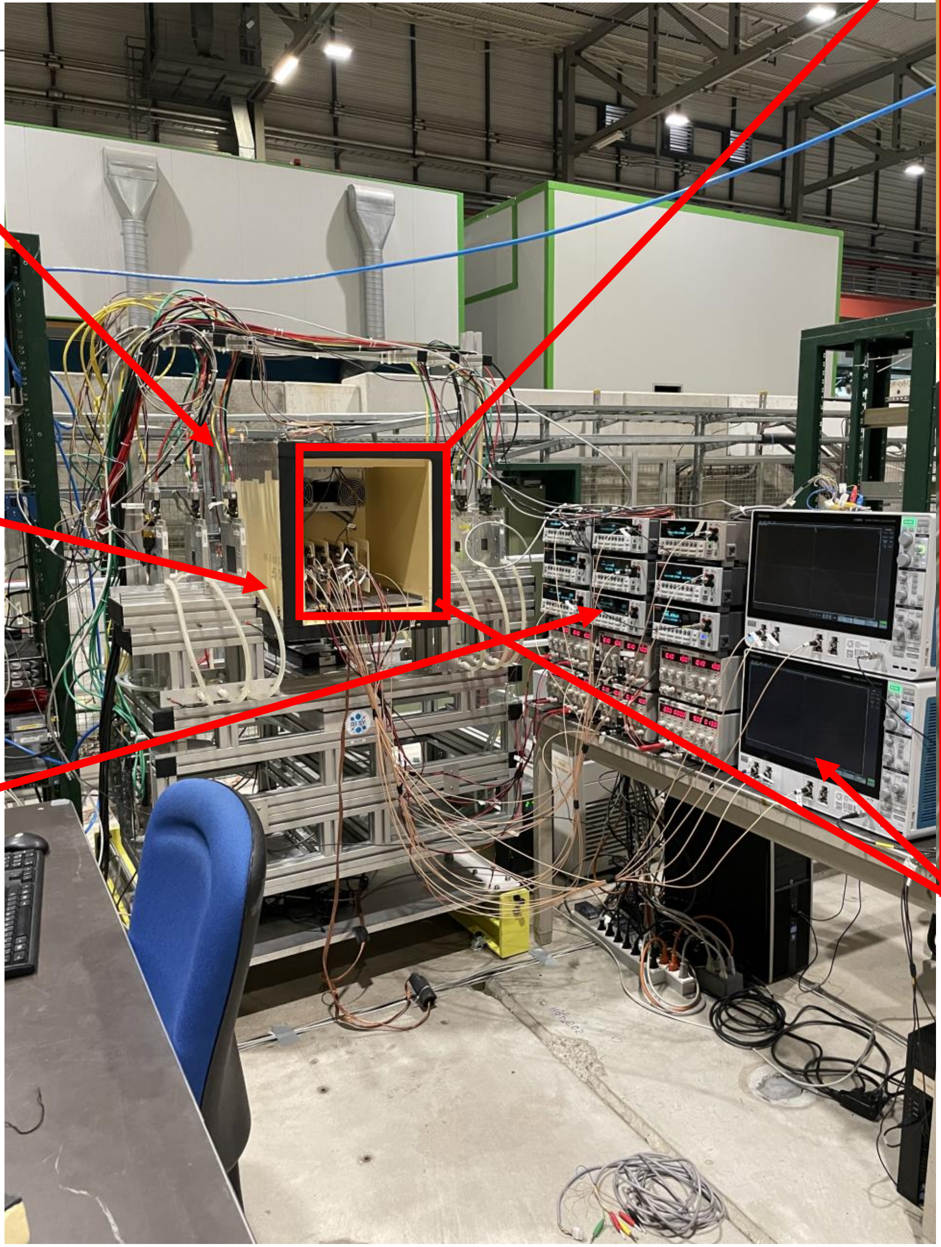
HV 1 Keithley 2400/2410 HV 2 Keithley 2400/2410 HV 3 Keithley 2400/2410 HV 4 Keithley 2400/2410

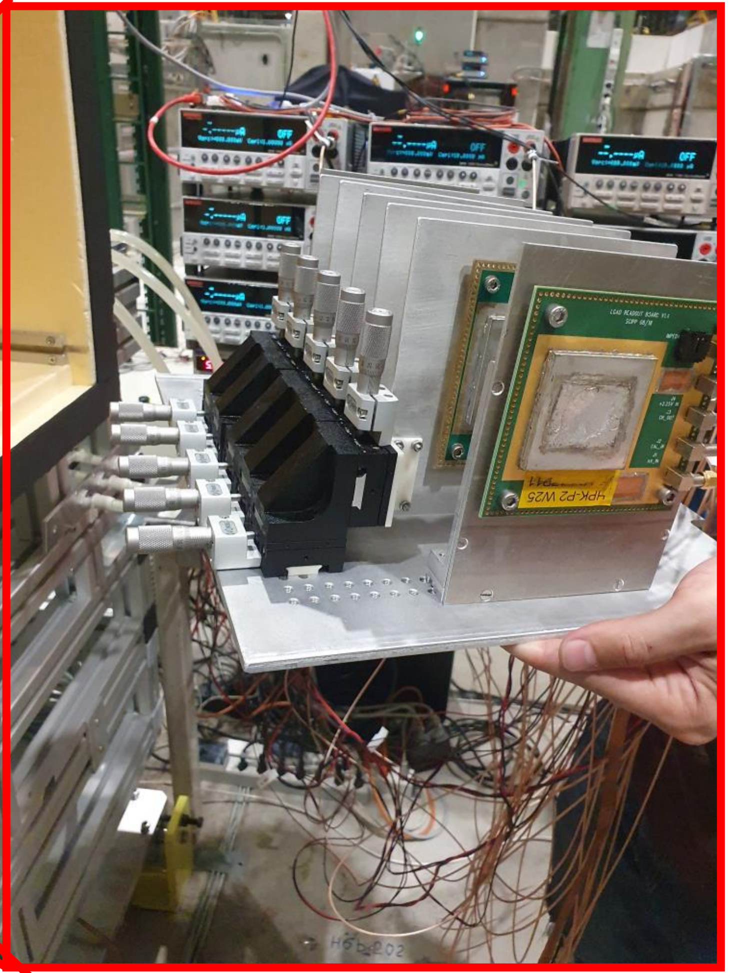
HV 5 Keithley 2400/2410 HV 6 Keithley 2400/2410 HV 7 Keithley 2400/2410

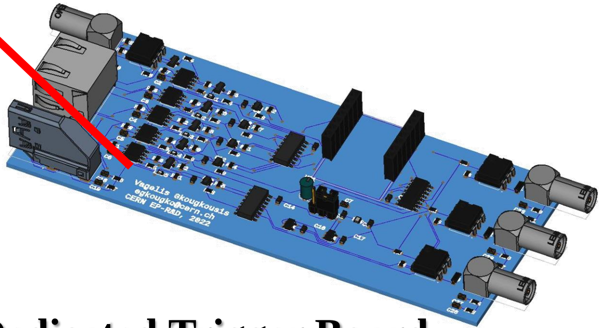
Created by: Vagelis Gkougkousis, 2021 egkougko@cern.ch

	GPIB Address	Start Voltage	End Voltage	Voltage Step	Repetitions	Compliance	Set Delay	Voltage	Current
HV1	Keithley2410A (IV Mode)	0.00 V	-100.00 V	-5.00 V	2	15.00 uA	1.00 s	0 +/- 0 V	0E+0 +/- 0E+0 A
HV2	Keithley2410B (IV mode 2)	0.00 V	-100.00 V	-5.00 V	2	15.00 uA	1.00 s	0 +/- 0 V	0E+0 +/- 0E+0 A
HV3	Keithley2410A (IV mode)	0.00 V	-100.00 V	-5.00 V	2	15.00 uA	1.00 s	0 +/- 0 V	0E+0 +/- 0E+0 A
HV4	Keithley2410B (IV mode 4)	0.00 V	-100.00 V	-5.00 V	2	15.00 uA	1.00 s	0 +/- 0 V	0E+0 +/- 0E+0 A
HV5	Keithley2410A (IV mode)	0.00 V	-100.00 V	-5.00 V	2	15.00 uA	1.00 s	0 +/- 0 V	0E+0 +/- 0E+0 A
HV6	Keithley2410B (IV mode 6)	0.00 V	-100.00 V	-5.00 V	2	15.00 uA	1.00 s	0 +/- 0 V	0E+0 +/- 0E+0 A
HV7	Keithley2410B (IV mode)	0.00 V	-100.00 V	-5.00 V	2	15.00 uA	1.00 s	0 +/- 0 V	0E+0 +/- 0E+0 A

Slow Control DAQ

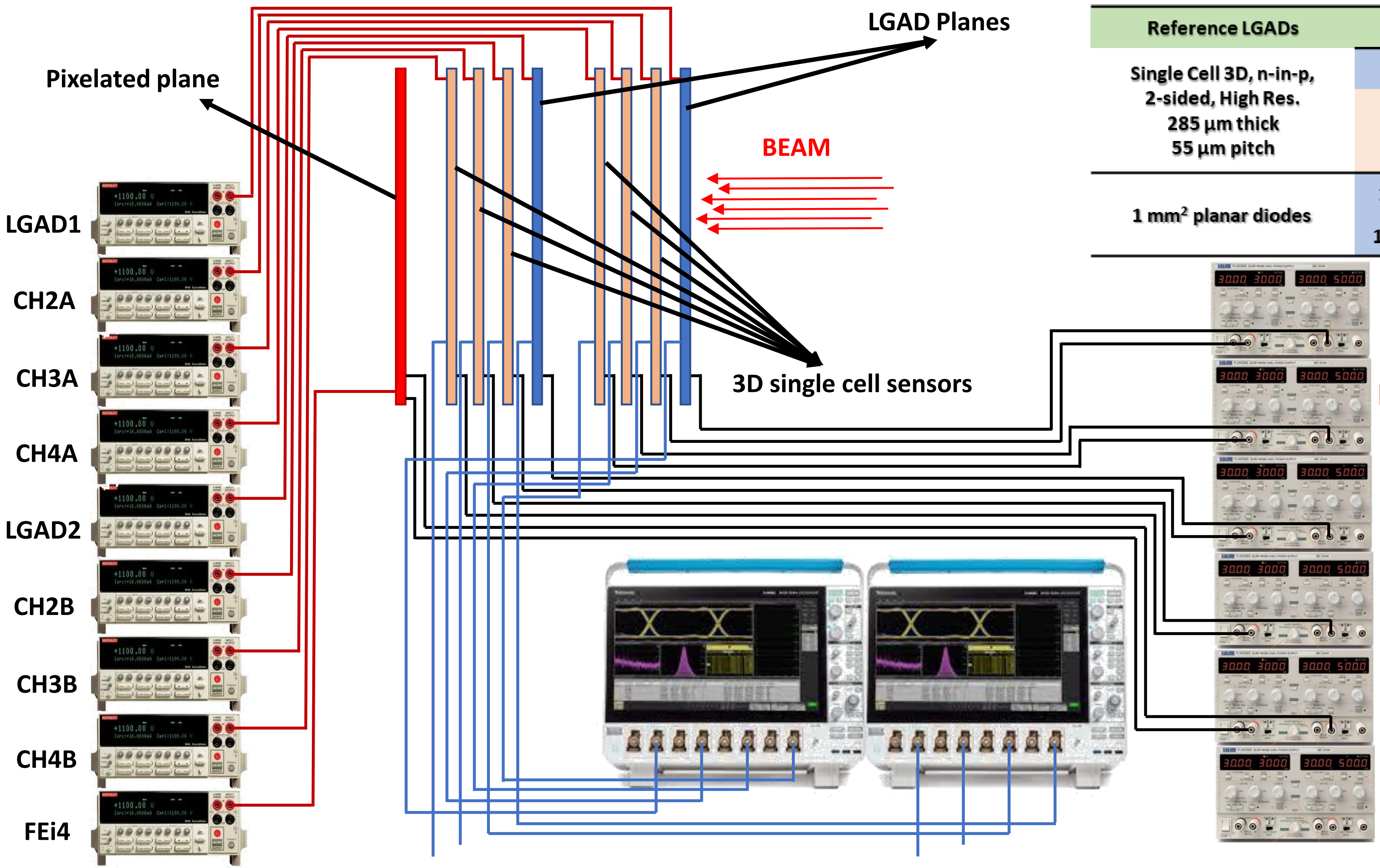






Dedicated Trigger Board

•Test Beam Configuration



LGAD Planes

Pixelated plane

BEAM

3D single cell sensors

LGAD1

CH2A

CH3A

CH4A

LGAD2

CH2B

CH3B

CH4B

FEi4

June Test Beam Planning

Sample type	Sample no.	Fluence (n_{eq}/cm^2)
Reference LGADs	2	Unirradiated
Single Cell 3D, n-in-p, 2-sided, High Res. 285 µm thick 55 µm pitch	1	Unirradiated
	1	1×10^{15}
	1	8×10^{15}
1 mm² planar diodes	1 x 50 µm thick	Unirradiated
	1 x 100 µm thick	Unirradiated

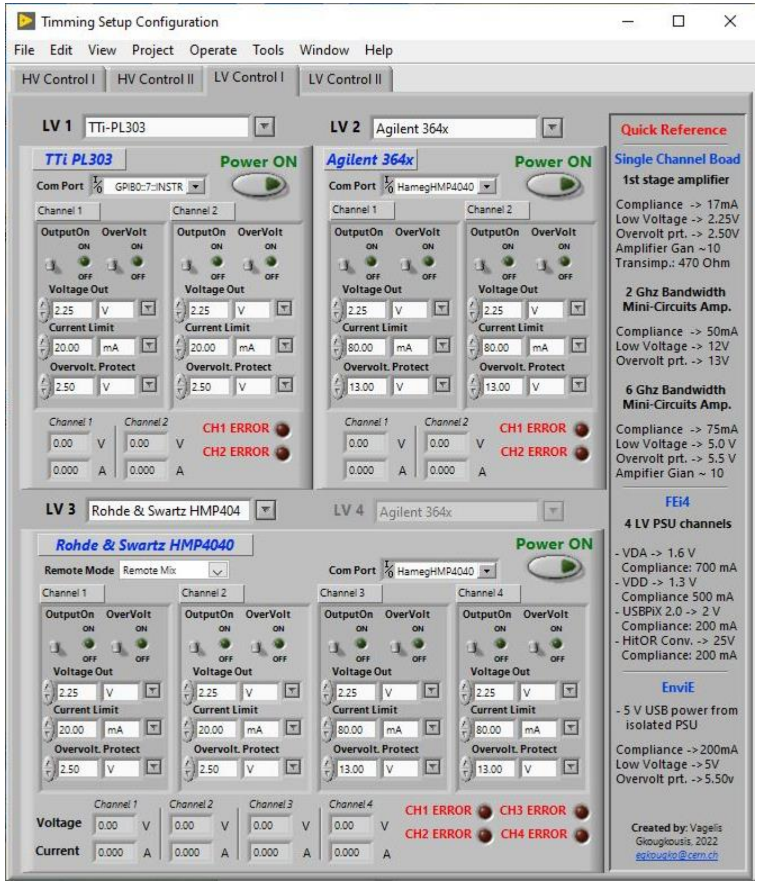
Equipment List

- 2 x Oscilloscopes
- 9 x Keithley 2410
- 6 x TTi PL303
- 8 Second stage amplifiers
- 6 micro-positioning stages
- Humidity – Temperature monitoring system (EnViE)
- Cold Box for -20°C operation
- Trigger Interface Board V2.0
- SMA Cables

•HV & LV Control/monitoring

- Precompiled executable available on GitLab: here

Labview based


Timming Setup Configuration

File Edit View Project Operate Tools Window Help

HV Control I | HV Control II | LV Control I | LV Control II

LV 1 TTi-PL303 — TTi PL303 — Power ON — Com Port GPIB0::7::INSTR

LV 2 Agilent 364x — Agilent 364x — Power ON — Com Port HamegHMP4040

Channel 1 / Channel 2: OutputOn, OverVolt; Voltage Out 2.25 V; Current Limit 20.00 mA / 80.00 mA; Overvolt. Protect 2.50 V / 13.00 V

CH1 ERROR, CH2 ERROR

LV 3 Rohde & Swartz HMP404 — Rohde & Swartz HMP4040 — Power ON — Remote Mode Remote Mix — Com Port HamegHMP4040

LV 4 Agilent 364x

Channel 1 … Channel 4: Voltage Out 2.25 V; Current Limit 20.00 mA / 80.00 mA; Overvolt. Protect 2.50 V / 13.00 V

CH1 ERROR, CH2 ERROR, CH3 ERROR, CH4 ERROR

Quick Reference

Single Channel Boad

1st stage amplifier

Compliance -> 17mA
Low Voltage -> 2.25V
Overvolt prt. -> 2.50V
Amplifier Gan ~10
Transimp.: 470 Ohm

2 Ghz Bandwidth Mini-Circuits Amp.

Compliance -> 50mA
Low Voltage -> 12V
Overvolt prt. -> 13V

6 Ghz Bandwidth Mini-Circuits Amp.

Compliance -> 75mA
Low Voltage -> 5.0 V
Overvolt prt. -> 5.5 V
Ampifier Gian ~ 10

FEi4

4 LV PSU channels

- VDA -> 1.6 V
  Compliance: 700 mA
- VDD -> 1.3 V
  Compliance 500 mA
- USBPiX 2.0 -> 2 V
  Compliance: 200 mA
- HitOR Conv. -> 25V
  Compliance: 200 mA

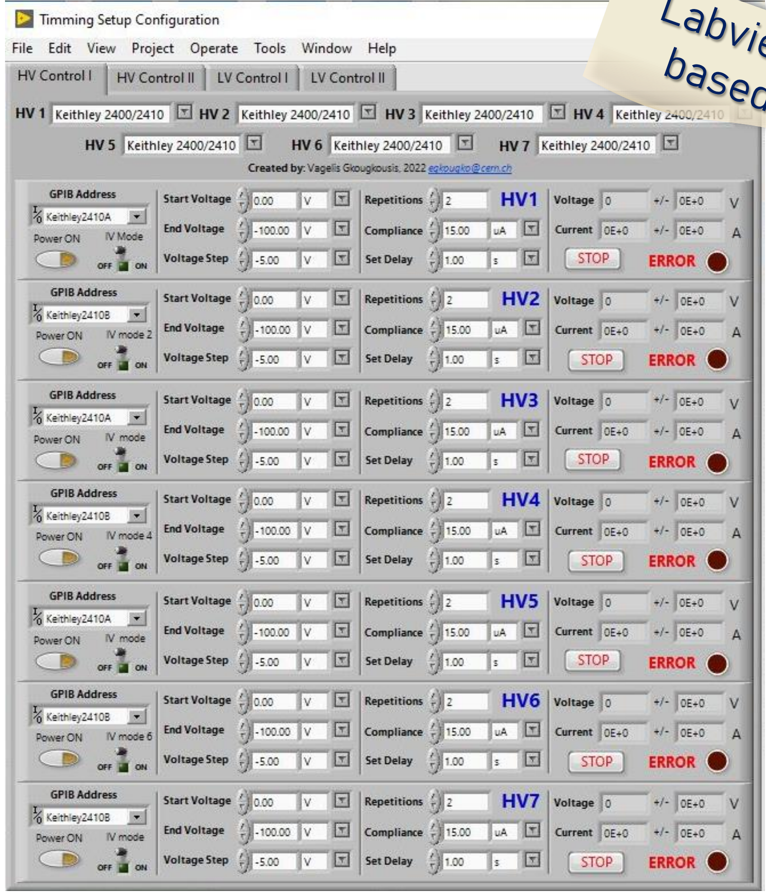
EnviE

- 5 V USB power from isolated PSU

Compliance ->200mA
Low Voltage ->5V
Overvolt prt. ->5.50v

Created by: Vagelis Gkougkousis, 2022
egkougko@cern.ch

Multi-model Support with Polymorphic UI


Timming Setup Configuration

File Edit View Project Operate Tools Window Help

HV Control I | HV Control II | LV Control I | LV Control II

HV 1 Keithley 2400/2410 HV 2 Keithley 2400/2410 HV 3 Keithley 2400/2410 HV 4 Keithley 2400/2410
HV 5 Keithley 2400/2410 HV 6 Keithley 2400/2410 HV 7 Keithley 2400/2410

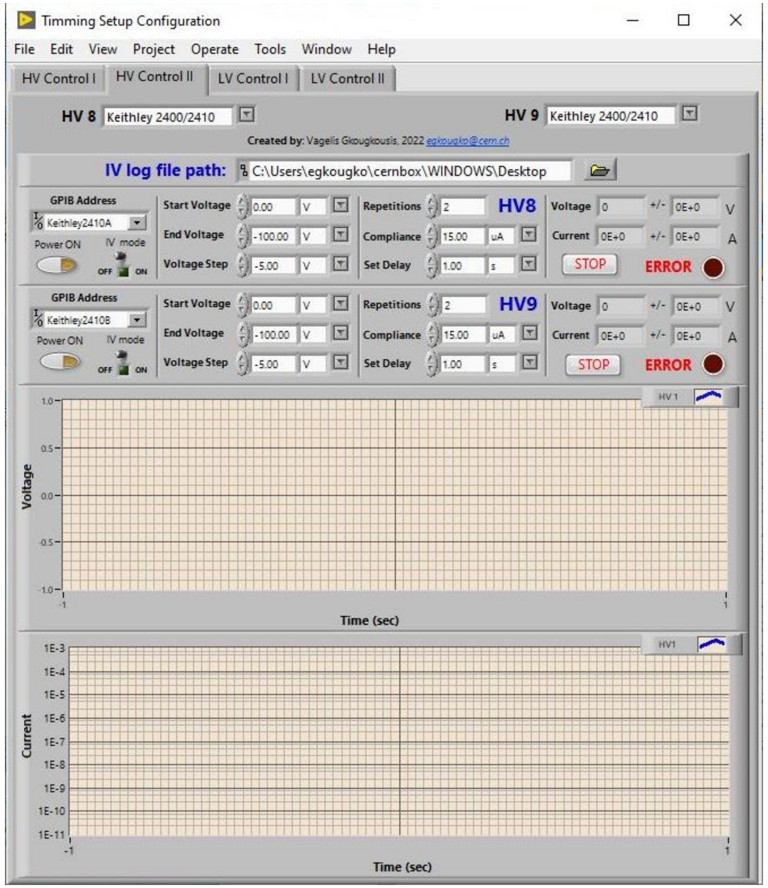
Created by: Vagelis Gkougkousis, 2022 egkougko@cern.ch

HV1 … HV7: GPIB Address Keithley2410A / Keithley2410B; Start Voltage 0.00 V; End Voltage -100.00 V; Voltage Step -5.00 V; Repetitions 2; Compliance 15.00 uA; Set Delay 1.00 s; Voltage 0 +/- 0E+0 V; Current 0E+0 +/- 0E+0 A; STOP; ERROR

High voltage

KEITHLEY

2400/2410 series


Timming Setup Configuration

File Edit View Project Operate Tools Window Help

HV Control I | HV Control II | LV Control I | LV Control II

HV 8 Keithley 2400/2410 HV 9 Keithley 2400/2410

Created by: Vagelis Gkougkousis, 2022 egkougko@cern.ch

IV log file path: C:\Users\egkougko\cernbox\WINDOWS\Desktop

HV8, HV9: GPIB Address Keithley2410A / Keithley2410B; Start Voltage 0.00 V; End Voltage -100.00 V; Voltage Step -5.00 V; Repetitions 2; Compliance 15.00 uA; Set Delay 1.00 s; Voltage 0 +/- 0E+0 V; Current 0E+0 +/- 0E+0 A; STOP; ERROR

Agilent Technologies

363X series

KEYSIGHT TECHNOLOGIES

364X series

ROHDE&SCHWARZ

HMP4040

Aim TTi

PL330DP

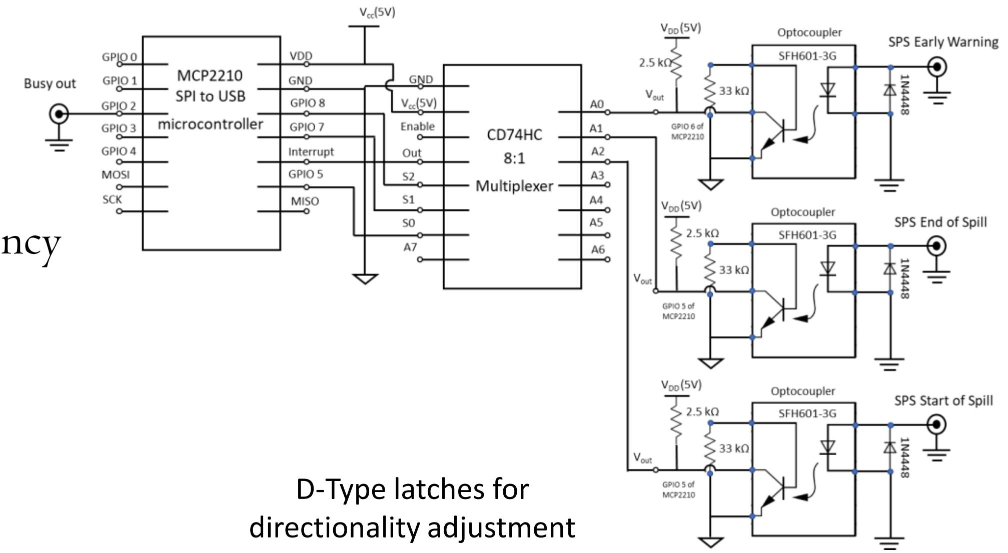
Aim TTi

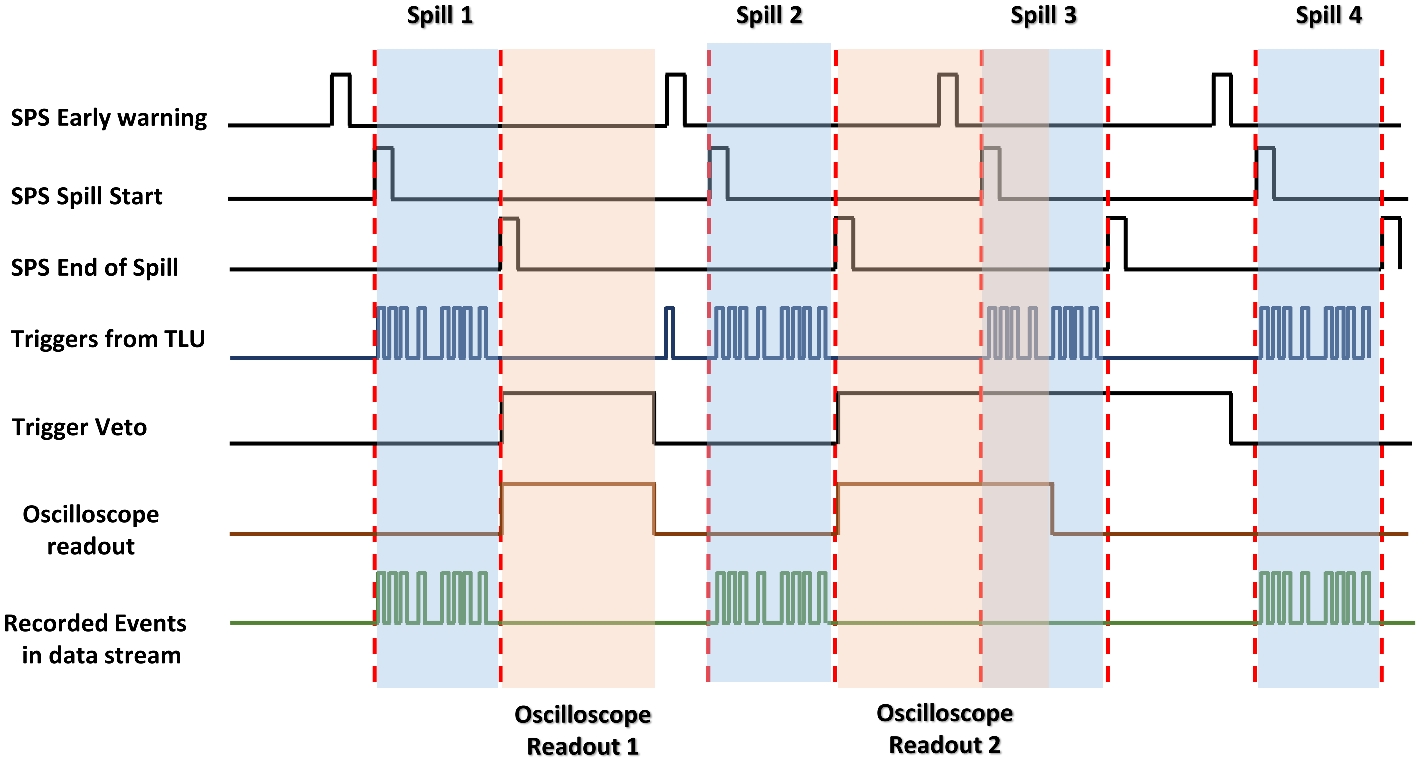
PL303QMD

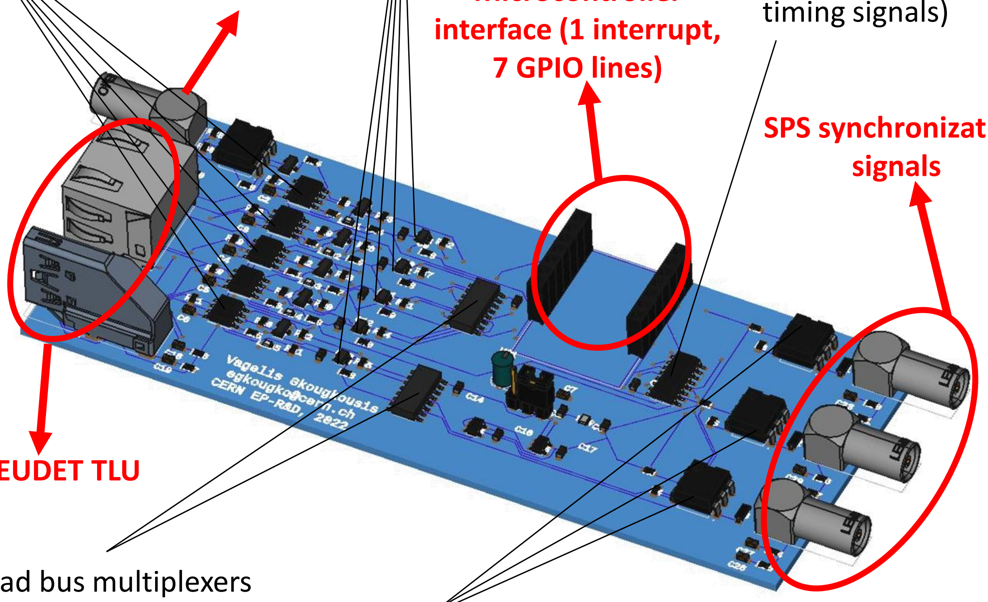
- 9x HV channels
- 16x LV channels
- Constant monitoring & logging
- Live protection

•Trigger Interface Board (TiB)

- Oscilloscope in fast readout mode with binary format
- Event readout only between SPS-spills or when event buffer full ti increase efficiency
- TLU Synchronization by vetoing data taking during read-out
- RJ-45 or HDMI for EUDET TLU communication (EUDET 2 compatible)
- Versatile design, I/Os Reconfigurable and microcontroller Reprogrammable via USB







D-Type latches for directionality adjustment

LVDS I/O Drivers

TTL Trigger out

Microcontroller interface (1 interrupt, 7 GPIO lines)

Interrupt multiplexer (cycle through input timing signals)

SPS synchronization signals

To EUDET TLU

Quad bus multiplexers (switch between setting and communication)

Input timing signal optocouplers

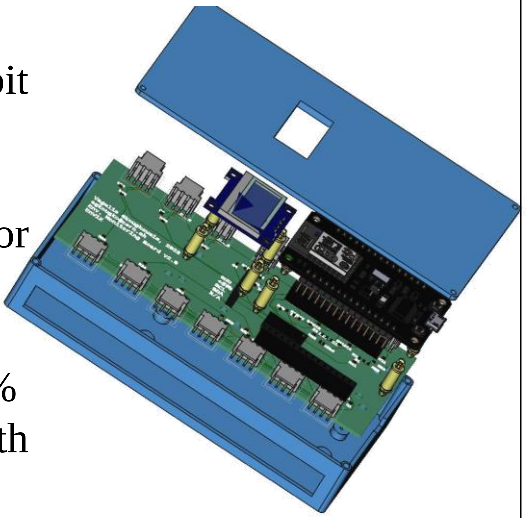
•Temperature Regulation

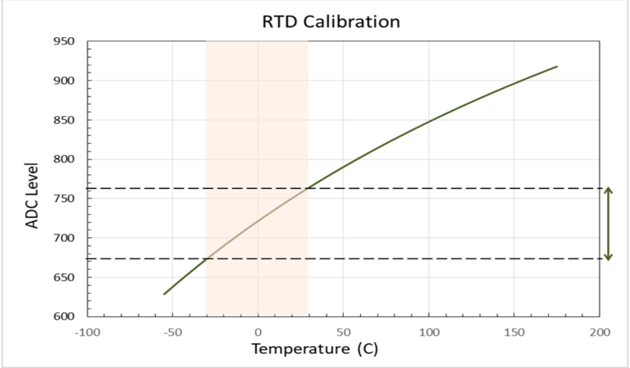
- Running at a crisp **-18 °C**
- Glycol cooling with temperature feedback - Labview control
- Humidity regulation though N_2 feeds

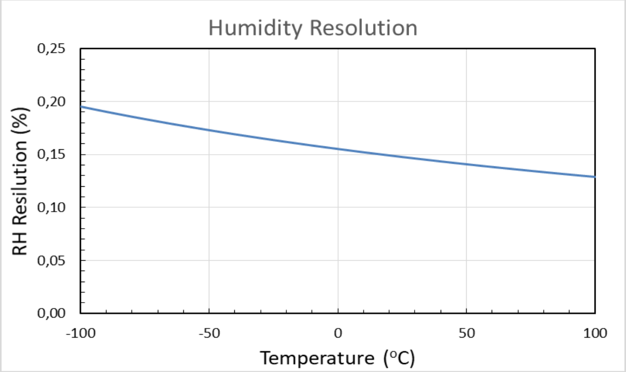
- EnviE GitLab with schematics: here

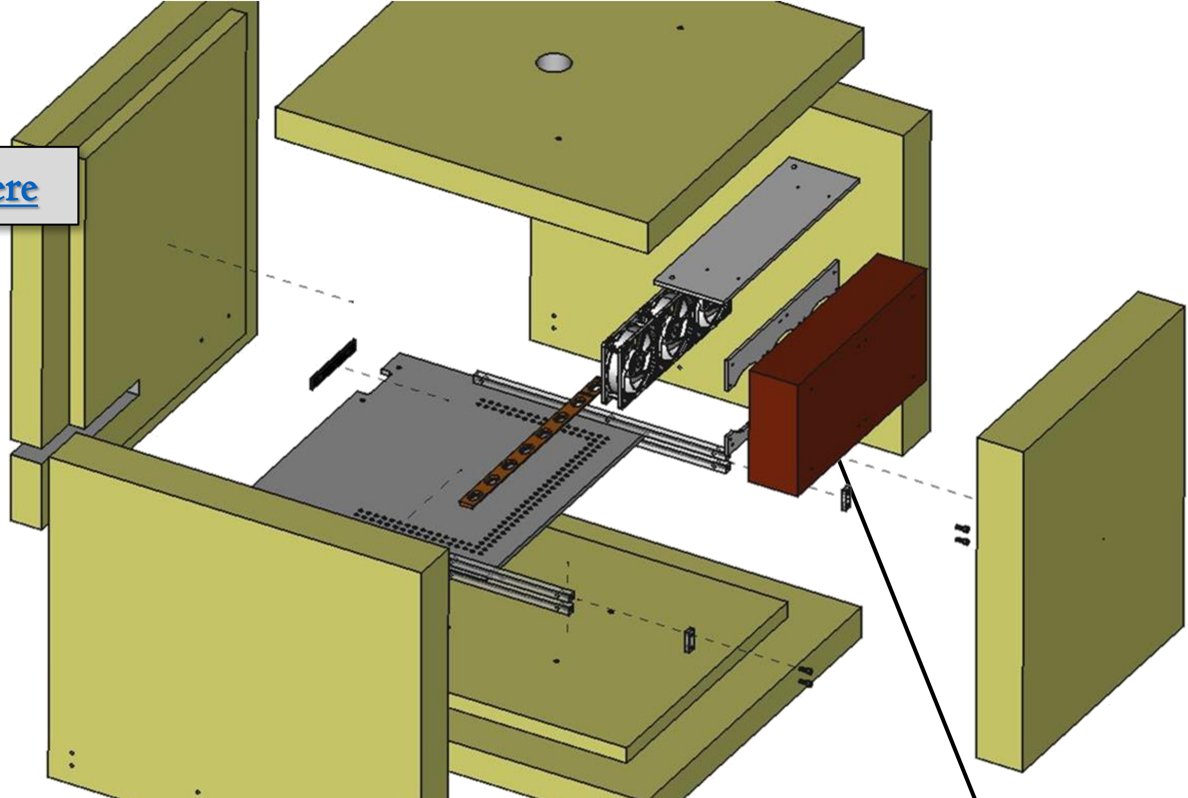
Environmental Expander V2.0 (EnviE)

- ESP8266 based with integrated 10-bit ADC, I2C and WiFi 802.11b
- Integrated OLED 128X64 pixel screen
- High precision voltage dividers and sensor decoupling
- ARDUINO / LoUA core web interface
- Temperature resolution of 0.8 °C ± 0.06 %
- Humidity resolution 0.1 % with temperature compensation









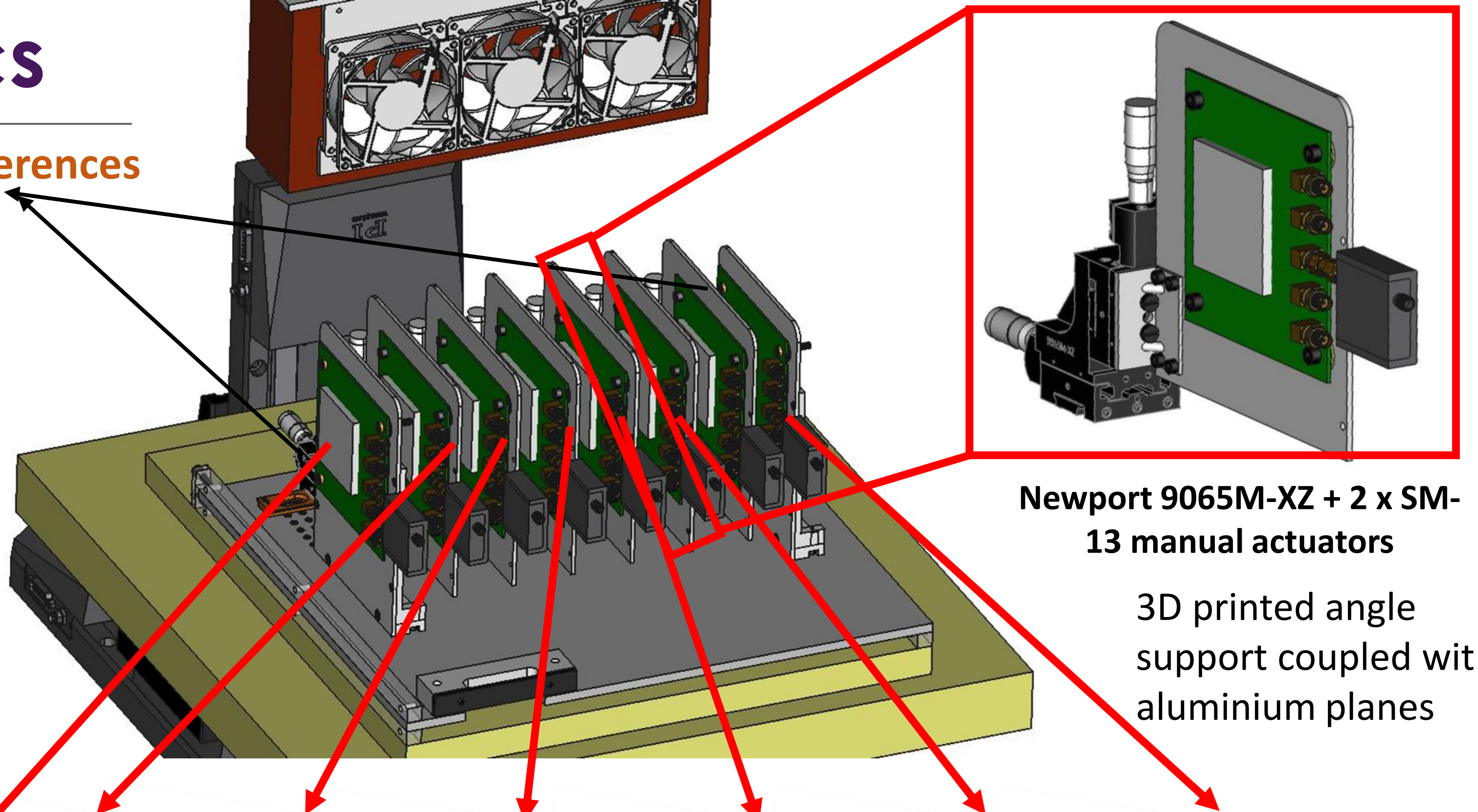
Water cooling block

- 6 c.m. thick XPS foam insulation
- Outer dimensions of 50 x 48 x 48 cm^3
- Use of commercial water-cooling block (link)
- 3 x Axial Fan DC 80x80x25mm 24V 111.6m^3/h – low remperature tested to -20°C (link)
- Total cost ~ 400 CHF

•Alignment & Mechanics

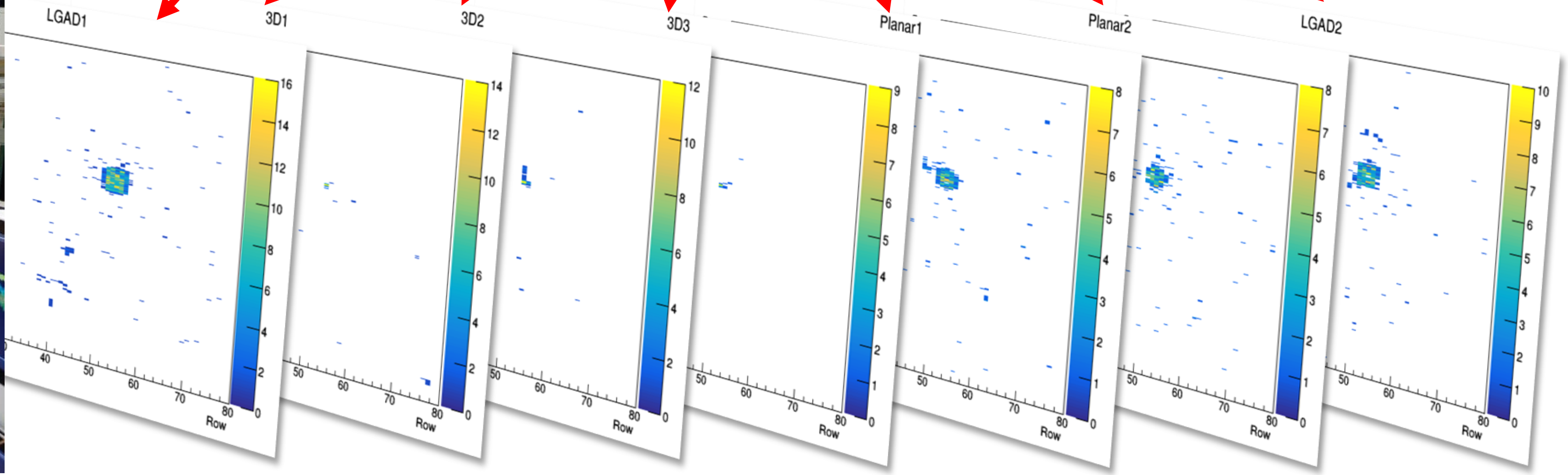
HPK LGAD Timing references

- Coincidences between DUTs and LGADs required for timing
- Alignment crucial to increase data efficiency
- Efficiency defined by largest overlapping region
- Micrometric on-line alignment using projections on FEi4 matrix
- ROI defined in addition to other trigger conditions

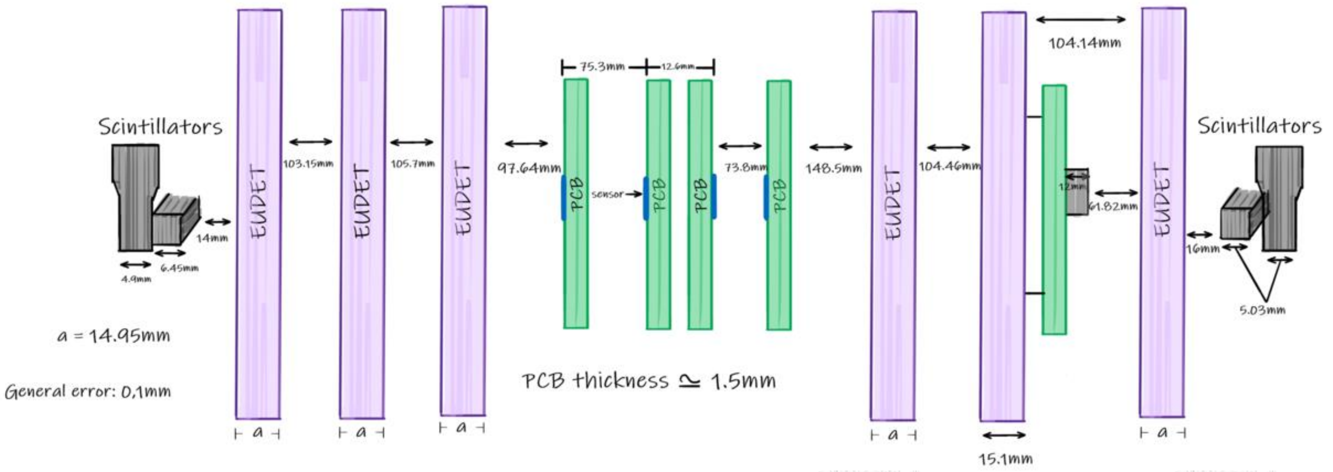


Newport 9065M-XZ + 2 x SM-13 manual actuators

3D printed angle support coupled with aluminium planes



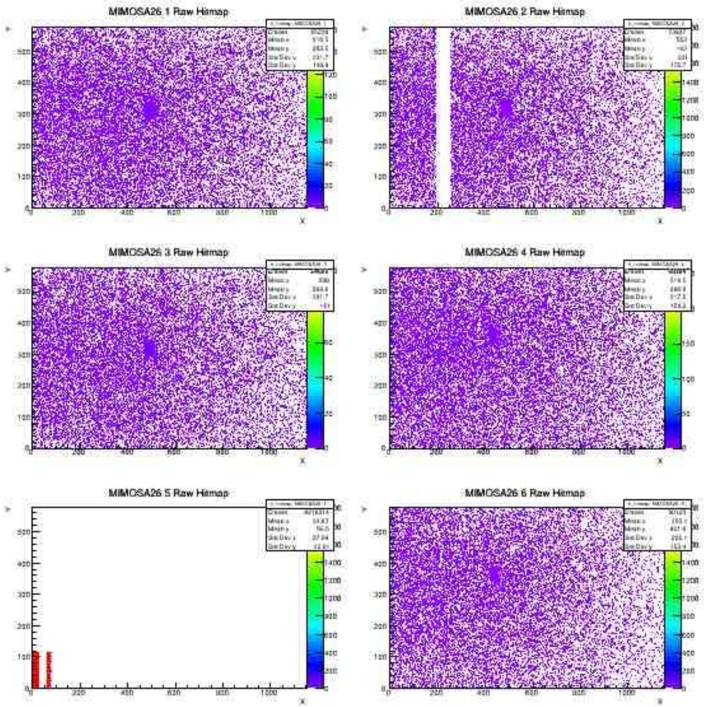
•Tracking and ROI

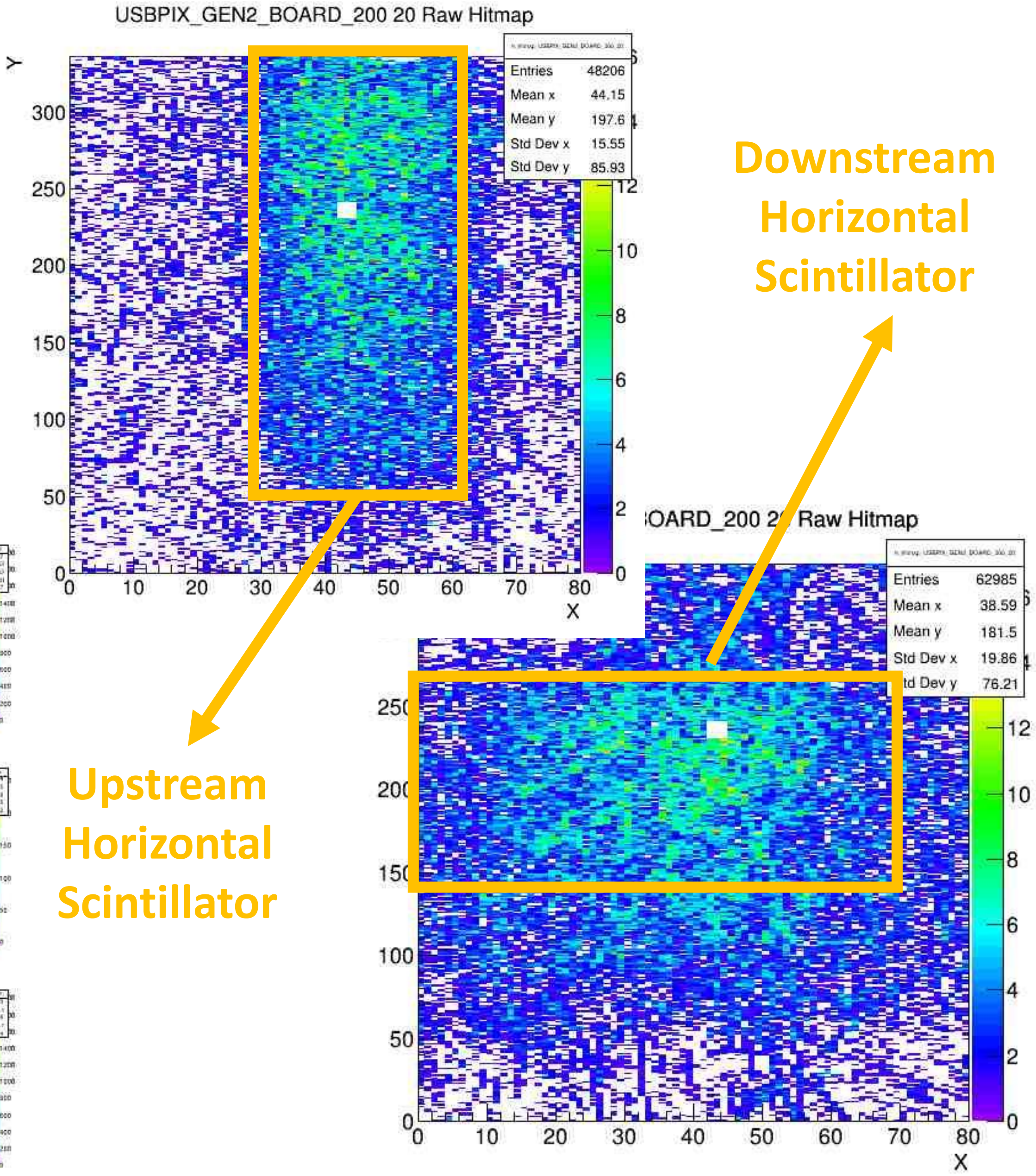


Telescope Planes

- **6 MIMOSA planes for tracking**
- **Plane no. 5 known to be bad**
- **Expected 5μm tracking resolution**
- **Estimated acquired number of events ~1M**

- Limited beam control as parasitic user
- Suffer from low intensity and low data rates of EUDAQ





Downstream Horizontal Scintillator

Upstream Horizontal Scintillator

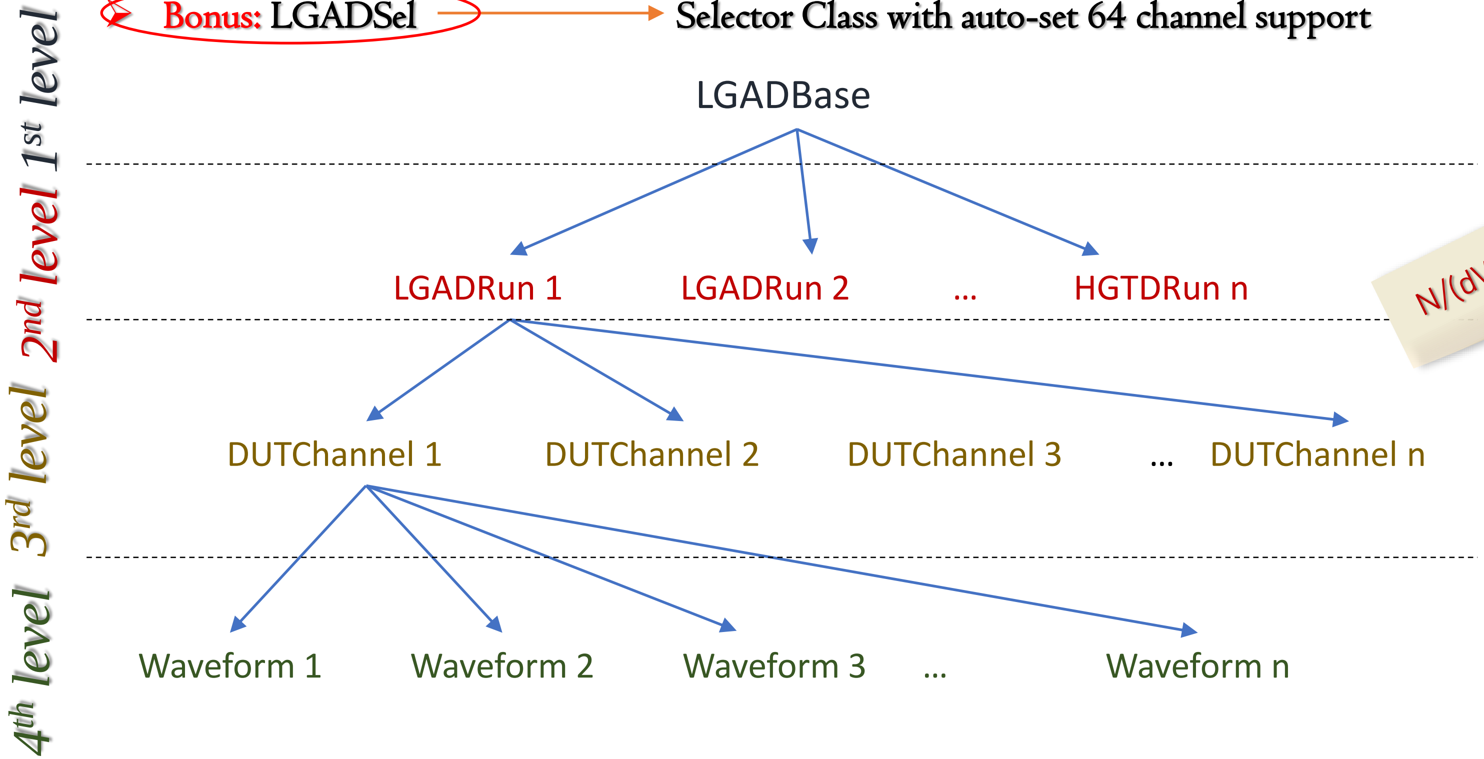
•Analysis Framework

- Code available on git: https://gitlab.cern.ch/egkougko/lgadutils

- Four main classes with dedicated header and implementation files, one wrapper class handling user interaction

LGADUtils	Wrapper to handle user I/O and pass arguments
LGADBase	Basic framework function and infastructure
LGADRun	Timing resolution, CFD maps, multi DUT operations
LGADChannel	Mean pulse shape, mean pulse properties form entire run
WaveForm	Single Waveform properties and time walk corrections
Bonus: LGADSel	**Selector Class with auto-set 64 channel support**

C++ 11



- Iterative re-fitting and re-binning algorithm
- Fitting of discrete and variable binning quantities
- Bayesian uncertainties at efficiency level
- Event by event FFT transimpedance correction

N/(dV/dt) , T_{Rise}/SNR

Quantity	**Applied Fit type**
Min, Max voltage :	Gauss, Gauss x Landau fit
Start, stop, min, max indices :	Gauss, Gaussian fit
Noise / pedestal :	Gaussian fit
Min, Max, Rise, Trigger time :	Gaussian fit
Charge, dV/dT, Jitter, ToT:	Gauss x Landau fit
FFT:	Variable bin Gaussian

•Event by Event Strategy

File: WaveForm.cxx

- A four sequential step analysis approach
- Analysis escalates in a pyramid structure

Five preliminary sequential steps before we even start looking at the waveform

Step 1

Set Waveform values → Determine polarity → Find max, min point → Find start, stop point → Determine if noise → Determine if pulse within window

Step 2

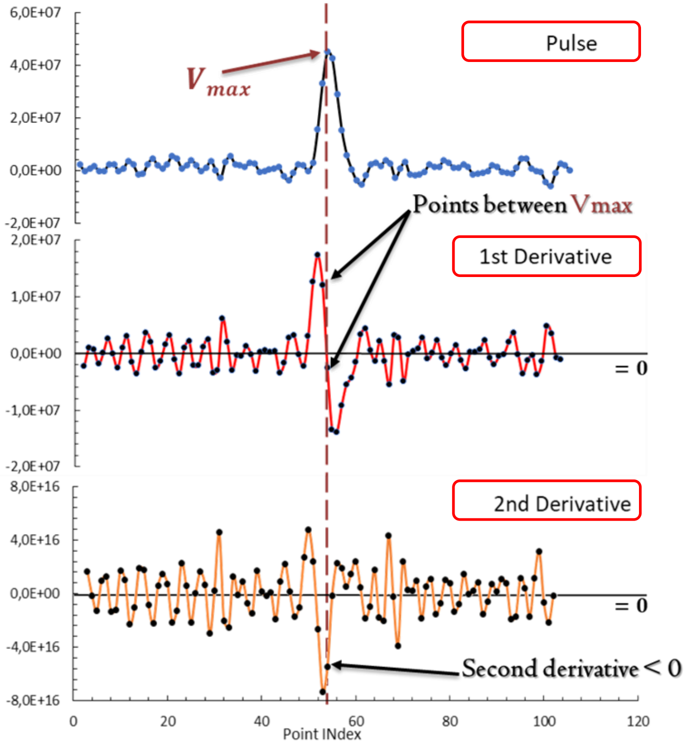
Define noise points → Use Gaussian fit for noise/Pedestal → Pedestal subtraction/ inversion → Recalculate start, stop points, min, max

Step 3

Compute charge → Determine rise time → Determine CFD Time → Compute dV/dT → Determine Trigger Time → Estimate Trigger & CFD ToT

Step 4

Perform CFD time to voltage Correction (Time Walk) → Signal FFT → Noise FFT



- If $SD_{maxima} > SD_{minima}$
  $D_m(max) > D_m(min)$
  or $SD_{maxima} < 1.05*SD_{minima}$
  $D_m(max) > D_m(min)$

Positive polarity

IsNoise Algorithm

Number of points with $0.8 \cdot V_{max}$

- If $N_{points} > 2$ test 0.7 , 0.6 & $0.5 \cdot V_{max}$ to account for wavy waveforms
- If $N_{points} > 2$ then require $dN_{points} < 8/12/16/20$

•Iterative Re-fitter & signal templates

File: LGADFits.cxx

- ➢ Centralized fitter engine for all fits
- ➢ Fully automated, including limits, method and Minuit minimization
- ➢ 36 Iterations per fit with limits and bin size variation to determine best combination
- ➢ Over-binning protection, automatic variable discreetness test
- ➢ Variable binning for FFT, frequency histograms
- ➢ Supported ROOFit, Standalone Minuit, Integral optimization or Shape

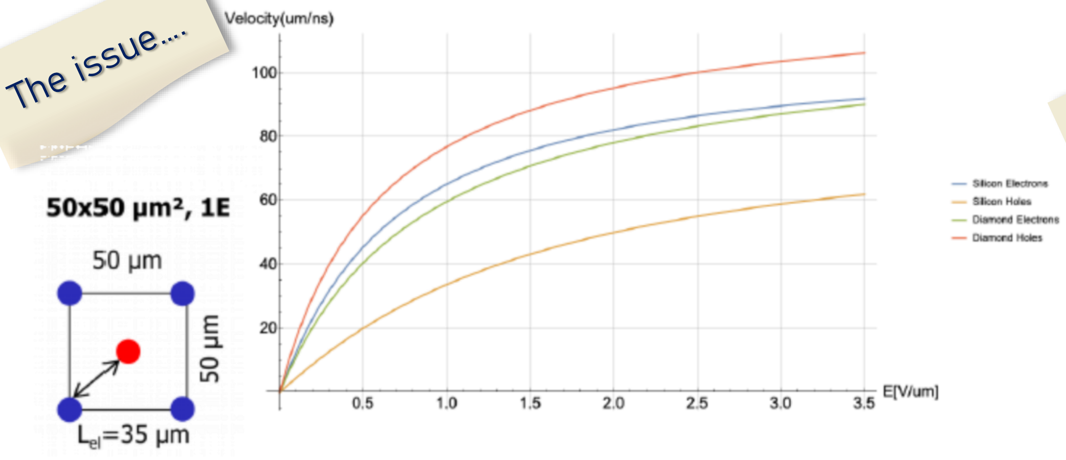
Dataset Type	Statistic Categorization	Bin Selection Criteria		
		Lower 3 bin number variations	Optimum Bin number	Higher 3 bin number variations
Discrete Datasets	$\frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma} < \sqrt{N_{elements}} < N_{bins\_max}$	$\left\lceil \left\lceil \sqrt{N_{elements}} \right\rceil - n \times \left\lceil \frac{\sqrt{N_{elements}} - \frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma}}{3} \right\rceil \right\rceil$ with 1 < n < 3	$\left\lceil \sqrt{N_{elements}} \right\rceil$	$\left\lfloor \left\lceil \sqrt{N_{elements}} \right\rceil + n \times \left\lceil \frac{N_{bins\_max} - \sqrt{N_{elements}}}{3} \right\rceil \right\rfloor$ with 1 < n < 3 **
		Lowest bin number	Rest of the bin number array	
	$\sqrt{N_{elements}} \leq \frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma} < N_{bins\_max}$	$\left\lfloor \sqrt{N_{elements}} \right\rfloor$	$\left\lfloor \sqrt{N_{elements}} \right\rfloor + n \times \left\lceil \lvert N_{bins\_max} - \sqrt{N_{elements}} \rvert / 6 \right\rceil$ with 1 < n < 6 **	
	$\sqrt{N_{elements}} \leq N_{bins\_max} < \frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma}$			
	$N_{bins\_max} \leq \sqrt{N_{elements}}$	$n \times \left\lfloor N_{bins\_max} / 7 \right\rfloor$ with 1 < n < 7		
Continuous Datasets		Lower 3 bin number variations	Optimum Bin number	Higher 3 bin number variations
	$\frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma} < \sqrt{N_{elements}}$	$\left\lceil \left\lceil \sqrt{N_{elements}} \right\rceil - n \times \left\lceil \frac{\sqrt{N_{elements}} - \frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma}}{3} \right\rceil \right\rceil$ with 1 < n < 3	$\left\lceil \sqrt{N_{elements}} \right\rceil$	$\left\lfloor \left\lceil \sqrt{N_{elements}} \right\rceil + n \times \left\lfloor \frac{\frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma}}{3} \right\rfloor \right\rfloor$ with 1 < n < 3
	$\sqrt{N_{elements}} \leq \frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma}$	$\left\lceil \left\lceil \frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma} \right\rceil - n \times \left\lceil \frac{\frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma} - \sqrt{N_{elements}}}{3} \right\rceil \right\rceil$ with 1 < n < 3	$\left\lceil \frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma} \right\rceil$	$\left\lfloor \frac{\lvert \lim_{fit} High - \lim_{fit} Low \rvert}{\sigma} + n \times \left\lfloor \frac{\sqrt{N_{elements}}}{3} \right\rfloor \right\rfloor$ with 1 < n < 3

Template Method

- ➢ Point by Point projection of all time-walk corrected (though CFD) signal pulses
- ➢ Landau X Gauss fit on projected point by point distribution
- ➢ Extraction of a "characteristic" signal composed of the MPVs of the Point by point projection fits
- ➢ RooKeyPdf for analytical description of signal
- ➢ Re-iteration on all events and fit of each waveform with the extrapolated analytical signal description
- ➢ Re-caclculate all quantities

•16 Channel Board

The issue….



- Assuming a linear filed dependence and a -15 V operation point at 35 µm column distance:

$$|E| \cong 0.43\ V/\mu m$$

- Estimating drift velocity for electrons:

$$v^e_{drift} = \frac{\mu_{0,e} \times E}{\left[1 + \left(\frac{\mu_{0,e} \times E}{v^e_{sat.}}\right)^{\beta_e}\right]^{1/\beta_e}}$$

with $v^e_{sat.} = 107\ \mu m/ns,\ \mu_{0,e} = 1417 \frac{cm^2}{Vs}, \beta_e = 1.109$

$$v^e_{drift} \approx \mathbf{41.4}\ \mu m/ns$$

- Extrapolated Rise time and Frequency:

$$t_{Rise} \approx \frac{1}{3} \times t_s = \frac{1}{3} \times \frac{d/2}{v^e_{drift}} \approx 140\ psec \Rightarrow \boxed{\mathbf{2.3\ GHz}}$$

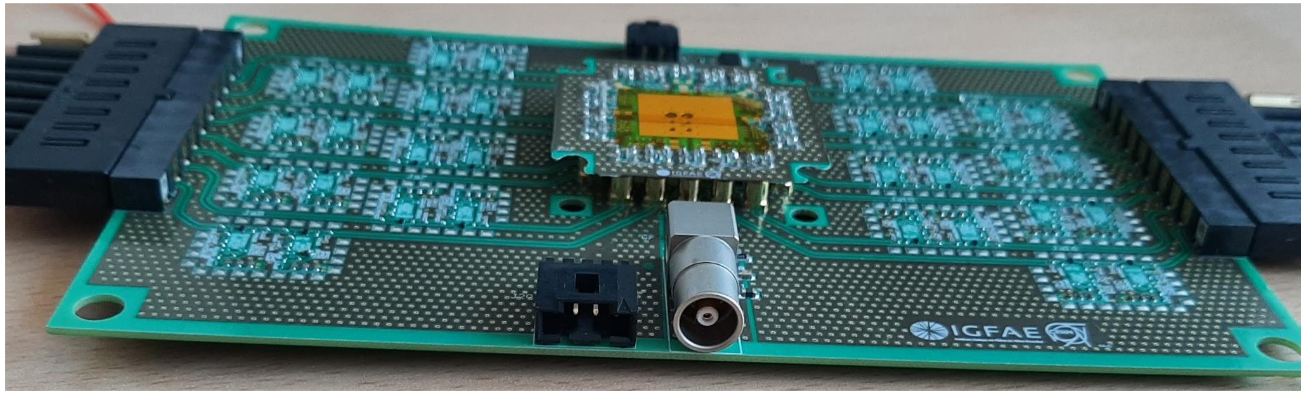
The solution

Timeline

July 2021 – Design submission
October 2021 – Initial tests
March 2022 – 2nd Mezzanine iteration
August 2022 – Test beam measurement with planar matrix

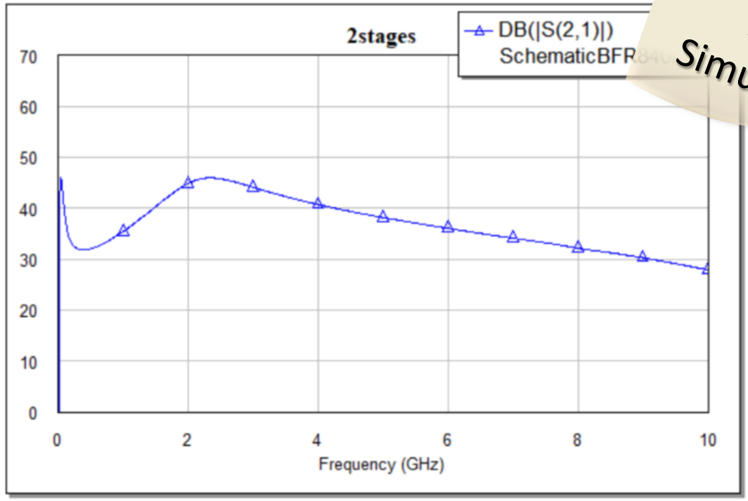
- ❖ High frequency multichannel versatile board
- ❖ Mezzanine design for fast sensor interchangeability
- ❖ Suitable for matrices (AC-LGAD applications) but also for single pad devices

- ➢ High Frequency SiGe discreate electronics @ 12 GHz bandwidth
- ➢ 2 Stage configuration with a transimpedance followed by a voltage stage
- ➢ Low max current (~10mA) with well behaved gain linearity vs V_{DD}
- ➢ Ruggers 3000 High Frequency substrate
- ➢ Pre-assembled miniaturized coaxial edge connectors with panel-mounted SMA plugs (1m cable length)
- ➢ 140 x140 mm outer dimensions



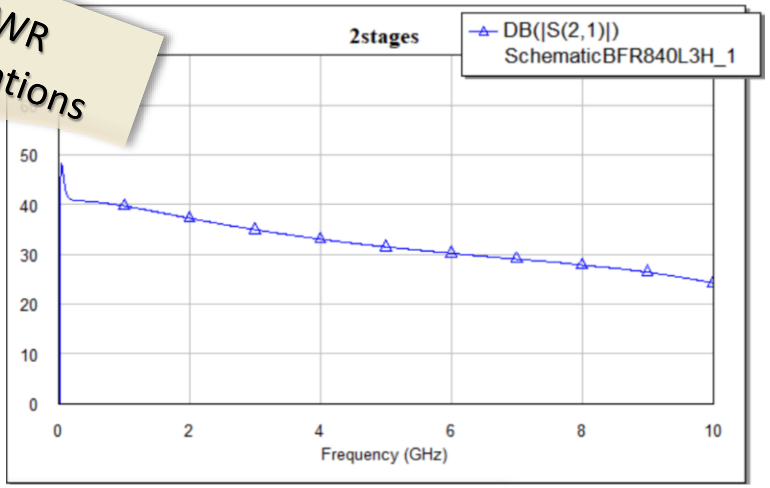
•Simulations and performance

Initial design



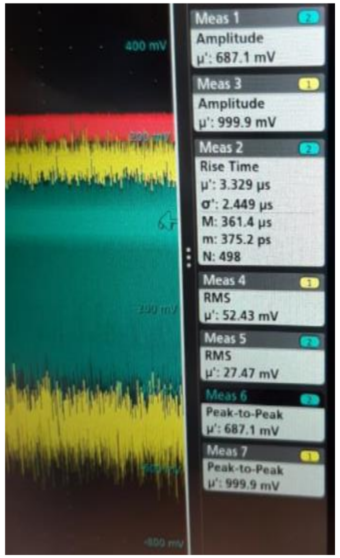
AWR Simulations

Modified –Uniform design



- ➢ Optimized design for uniform response with frequency
- ➢ No sharp gain change discontinuities
- ➢ No undershoot/overshoot observed
- ➢ Gain moderated to ~70 for a two-stage configuration
- ➢ 20% Higher SNR than UCSC board (with both stages)
- ➢ 2 x SNR with respect to UCSC board + niniCircuits second stage amplifier
- ➢ On going energy and transimpedance simulation

With signal injection



Meas 1 (2)
Amplitude
μ': 687.1 mV

Meas 3 (1)
Amplitude
μ': 999.9 mV

Meas 2 (2)
Rise Time
μ': 3.329 μs
σ': 2.449 μs
M: 361.4 μs
m: 375.2 ps
N: 498

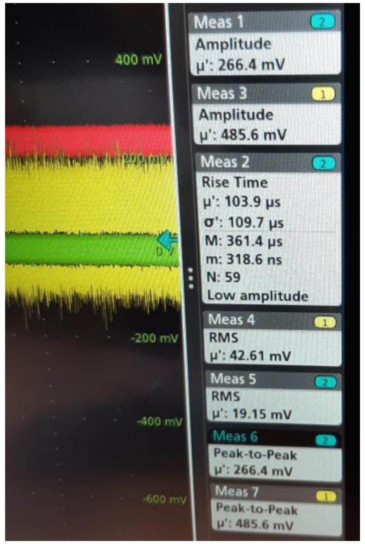
Meas 4 (1)
RMS
μ': 52.43 mV

Meas 5 (2)
RMS
μ': 27.47 mV

Meas 6 (2)
Peak-to-Peak
μ': 687.1 mV

Meas 7 (1)
Peak-to-Peak
μ': 999.9 mV

Without signal injection



Meas 1 (2)
Amplitude
μ': 266.4 mV

Meas 3 (1)
Amplitude
μ': 485.6 mV

Meas 2 (2)
Rise Time
μ': 103.9 μs
σ': 109.7 μs
M: 361.4 μs
m: 318.6 ns
N: 59
Low amplitude

Meas 4 (1)
RMS
μ': 42.61 mV

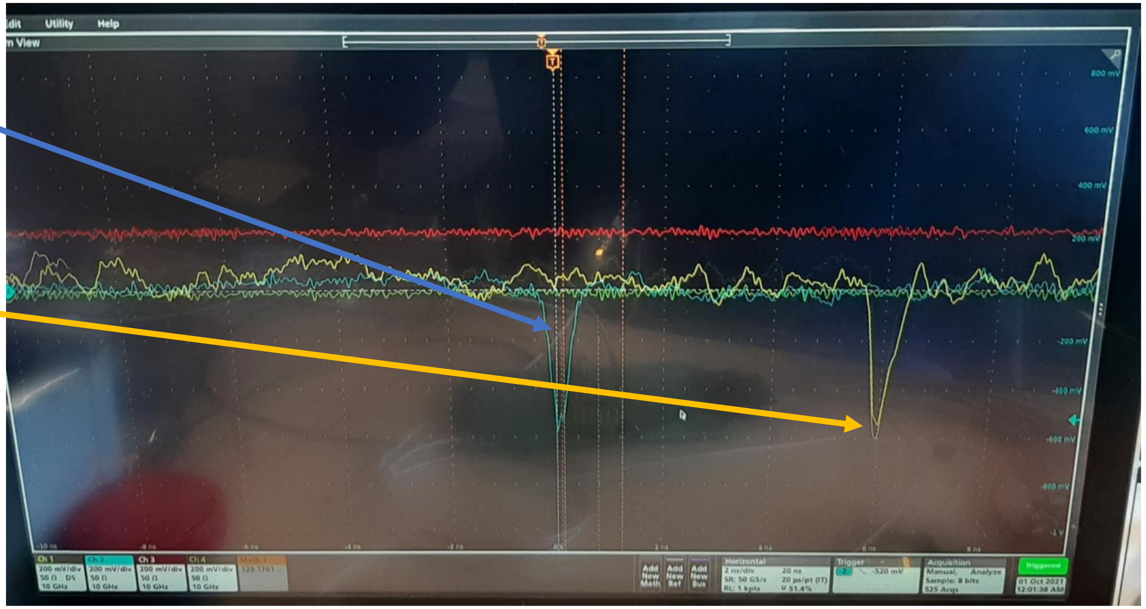
Meas 5 (2)
RMS
μ': 19.15 mV

Meas 6 (2)
Peak-to-Peak
μ': 266.4 mV

Meas 7 (1)
Peak-to-Peak
μ': 485.6 mV

Blue: 16 channel board

Yellow: UCSC board (only one stage)



•Towards the Future: Samplic

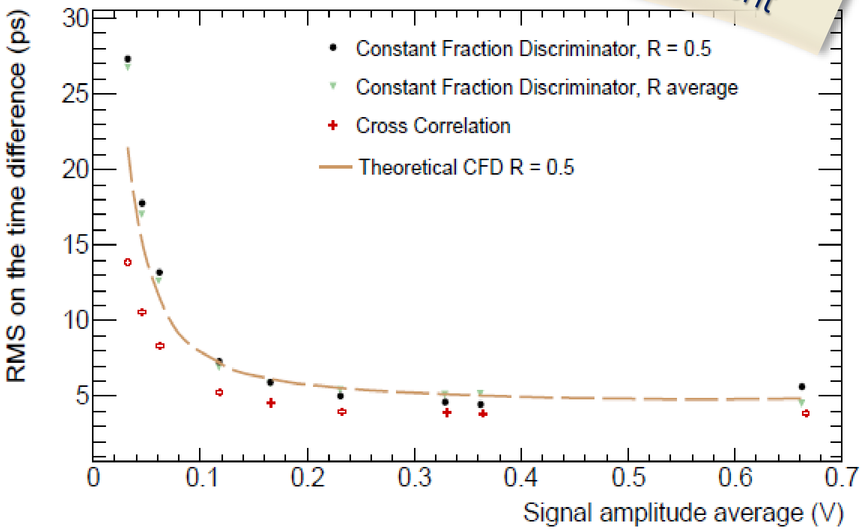
The ASIC (SAMPIC)

- Technology: AMS 0.18μm
- Sampling: between 3 and 8.4 GS/sec on 16 channels (depends on DAC setting)
- 16 channels per chip
- Signal Bandwidth of 1.6GHz
- Discrimination noise 2 mV, chip noise < 1.3 mV RMS
- Max input Signal: 1V unipolar (0.1V to 1.1V)

ADC

- 8 to 11 bit Wilkinson ADC at 1.3GHz
- Upon triggering 64 samples digitalized in parallel per channel
- Resolution adjustment possible to improve timing by reducing bit count
- Time resolution between 5 ps (calibrated) and 15ps (uncalibrated)

No minimum ToT Requirement



Calibration

- Calibration files provided for all operational points of the ADC
- Channel by channel calibration to be performed by user
- 64 channels x 4 operation points = 256 calibration runs

Connectivity

- USB2.0 + LabWindows based software (provided)
- UDP Based Ethernet, direct PC connection – no router support

•Conclusions

3D Pixels - Planar measurement campaign

- Several productions under investigation of different pixel size and thickness
- ***Estimate filed non-uniformity impact on time resolution vs pixel size***
- ***Determine minimal acceptable thickness for time resolution applications (SNR)***
- ***Investigate effects after irradiation up to 1e17 n_{eq}/cm^2 in protons and neutrons***

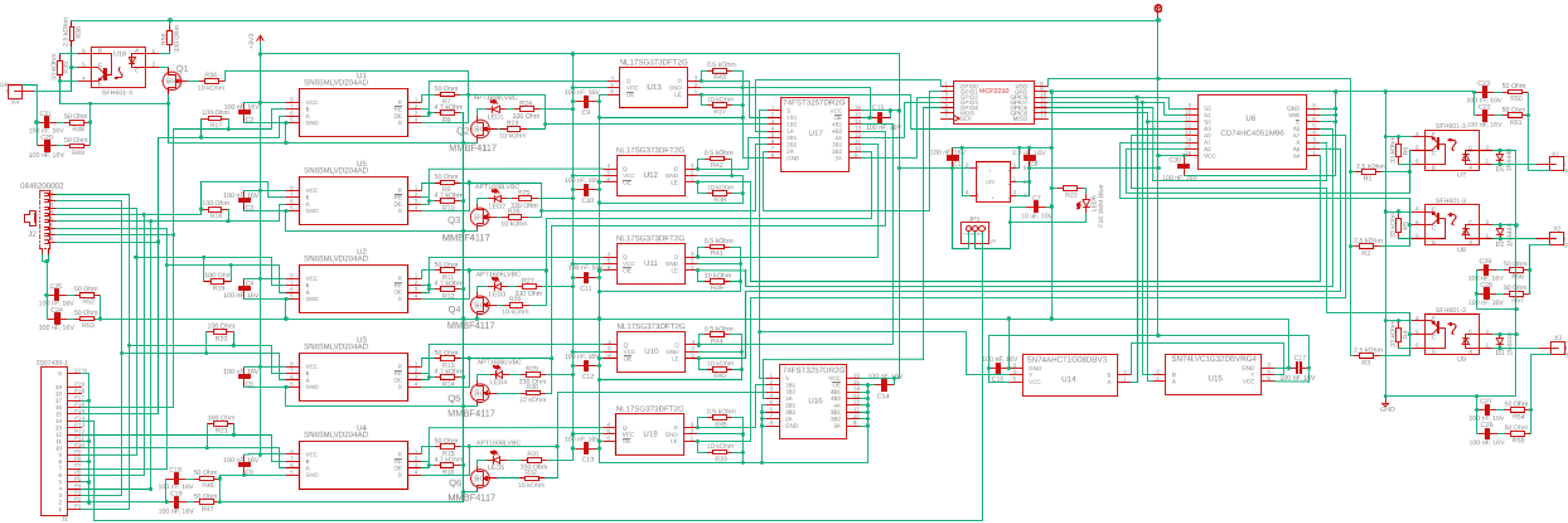
Primary Goals

Test-Beam Setup

- ***Trigger Interface board:*** Versatile, allows interfacing any acquisition instrument with EUDET
- ***Control Software:*** Polymorphic UI with seemingless multi-instrument support
- ***Cooling:*** XPS cold box with web interface temperature controllable system @ -18°C
- ***Mechanics:*** Micrometric alignment with individual DUT stages
- ***Analysis Framework:*** Advanced framework with signal shapes, iterative re-fitting and shape-based noise rejection

•Backup

•TIB Schematics



•Fits infrastructure

Available fitting options

File:
LGADFits.cxx

- ➢ Root multi-iterative automatic fitting for:

I. Gauss **II. Gauss X Landau**

```
int IterativeFit (std::vector<double> *w, std::pair<double, double> &gmean, std::pair<double, double> &gsigma,
                 TH1D* &FitHist, double &minchi2, std::string methode = "Gauss", std::pair<int, int> points =
                 std::make_pair(-1, -1))
```

- ➢ Unpinned 2-dimentional Linear fitting through RooFit and Minuit:

```
int LinearFit (std::vector<double>* vec, std::pair<double, double> &slope, std::pair<double, double> &intersept,
               std::vector<double>* vecErr = NULL);
```

- ➢ Roofit Convolution fitting (no iterative readjustment) for:

I. Gauss X Landau **II. Gauss X Linear**

```
int  RooConvFit  (std::vector<double>*  vec,  std::pair<double,  double>  &magMPV,  std::pair<double,  double>
                 &magSigma, std::string conv);
```

- ➢ Tow point linear interpolation:

```
double LinearInter(double x1, double y1, double x2, double y2, double y3);
```

- ➢ Fast Furrier transform algorithm: `double FFT(std::vector<double> *w, Long64_t snrate, int start, int stop);`

•Average pulse shape (RooFit)

Starting point, Non-optimized RooFit Convolution

I. Average calculated from 100 events

II. Each waveform is time aligned at 20% CFD

III. For all events, the same point of each waveform projected in TH1F
   - ✓ as many THIF as points in waveform
   - ✓ each with as many entries as events (100 here)

IV. Each TH1F fitted with a Landau X Gauss distribution

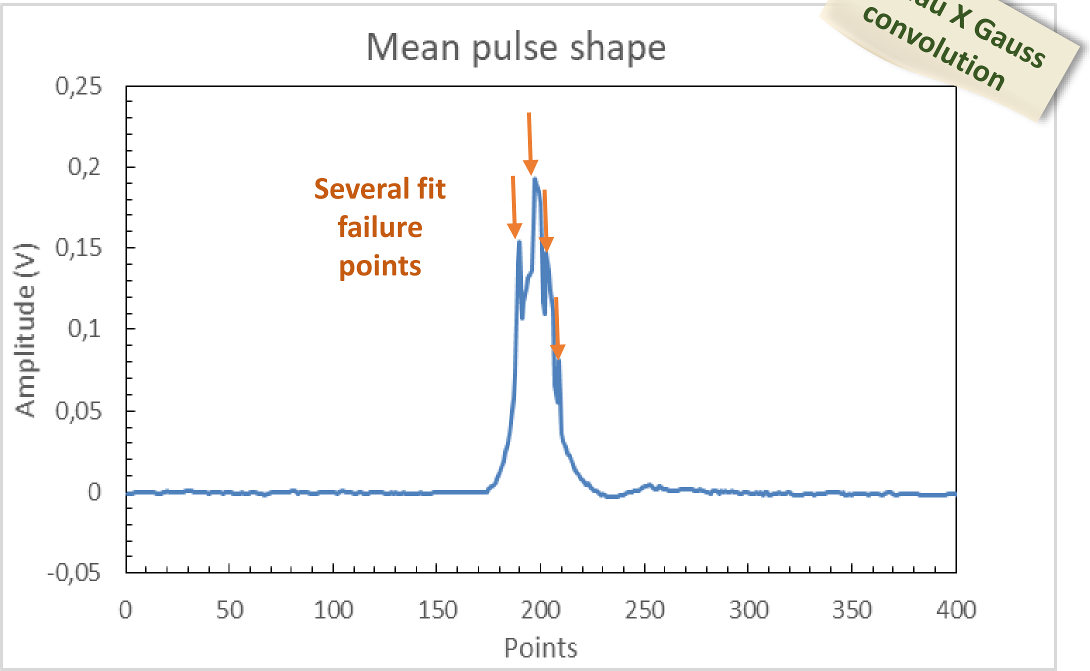
V. MPV, sigma and uncertainty extracted

VI. Fitting performed in RooFit using RooFit Convolution and Minuit

VII. No starting parameters or optimization

VIII. Plot the MPVs of each point in a single waveform

Landau X Gauss convolution



•Average pulse shape (RooFit)

Initial RooFit Optimization

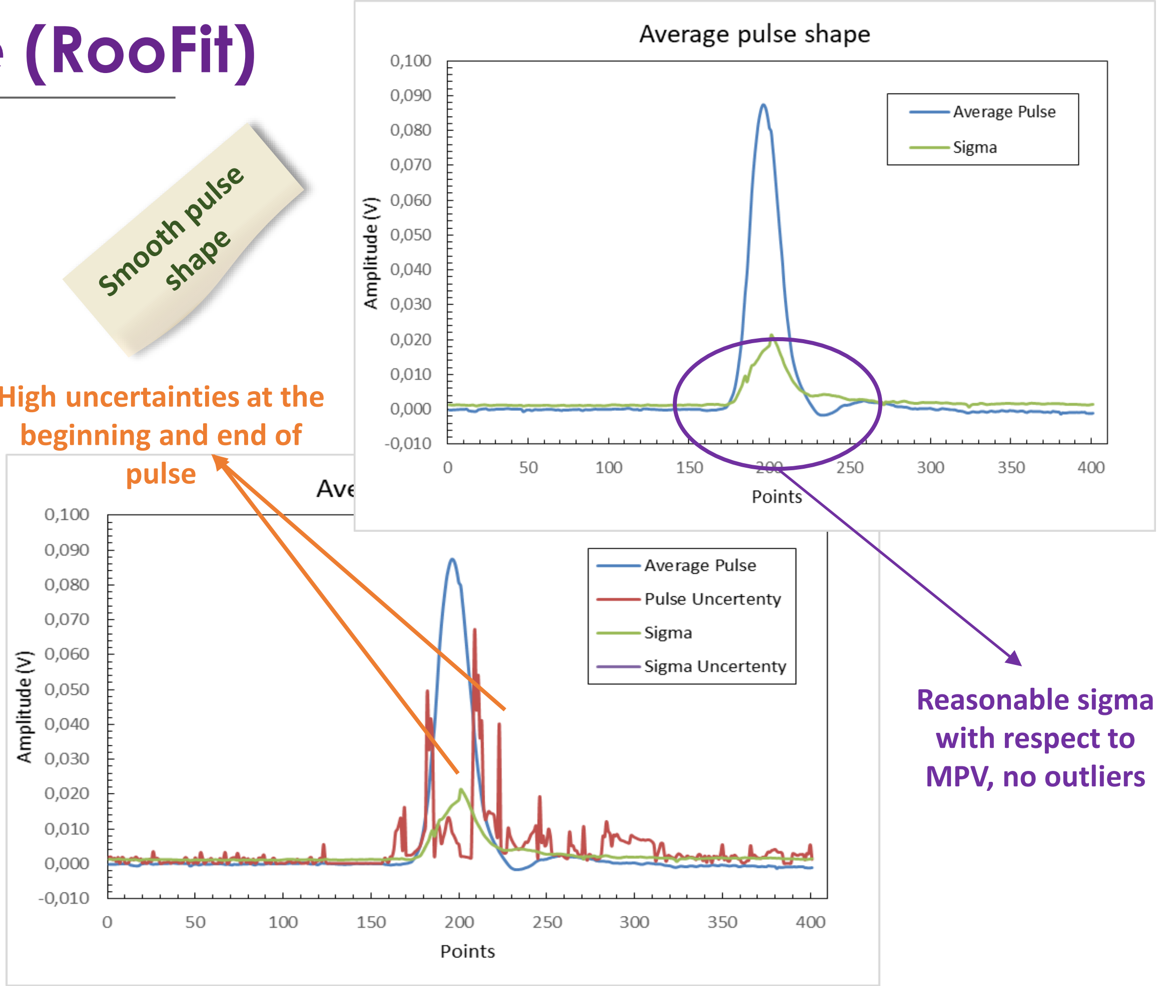
I. Fit Binning:
  - ✓ Symmetric fit limits: $\mathbf{x_{av.} \pm (5 \times \sigma)}$
  - ✓ Bin width defined as: $\boldsymbol{\sigma / 3}$
  - ✓ High statistics re-optimization, increase no. of bins if: $\mathbf{N_{points} > 1.5 \times N_{bins}}$

II. Parameter constraints:
  - ✓ Asymmetric limits for Landau MVP: $\mathbf{-4 \times |x_{RMS}| < x_{fit} < 2 \times | x_{RMS}|}$
  - ✓ Asymmetric limits for Landau sigma: $\mathbf{-0.001 \times \sigma < \sigma_{fit} < 2 \times \sigma}$
  - ✓ Symmetric limits for Gauss mean: $\mathbf{-2 \times \sigma < \sigma_{fit} < 2 \times \sigma}$

III. Parameter Initial values:
  - ✓ Landau **MPV** = $\mathbf{x_{RMS}}$
  - ✓ Gauss **sigma = 0**

IV. No re-iteration implementation

Smooth pulse shape



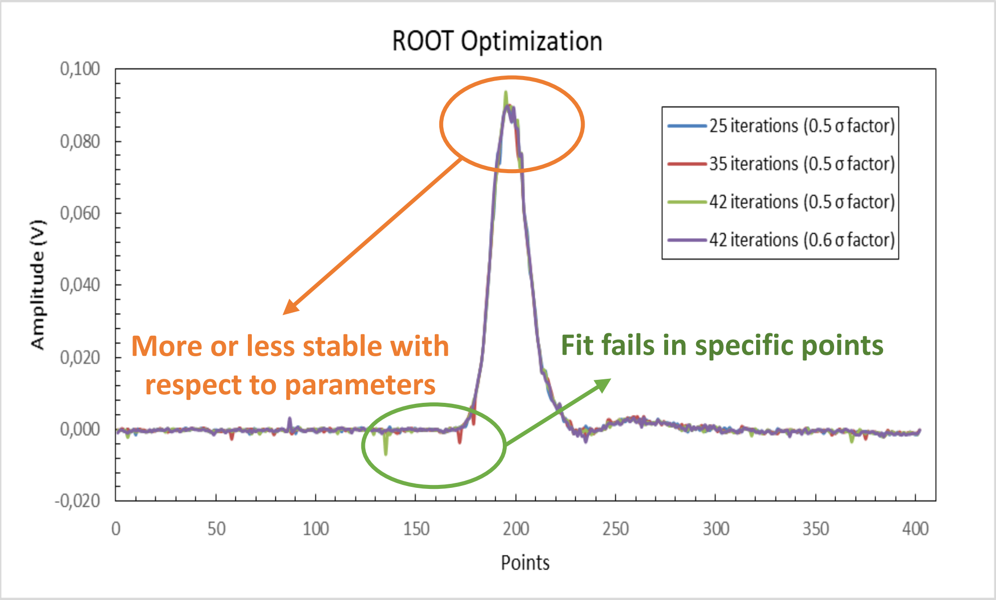
High uncertainties at the beginning and end of pulse

Reasonable sigma with respect to MPV, no outliers

•Average pulse shape (Root)

Root Optimization (no RooFit)

- Constraint parameter values but not fixed
- Manually defined convolution function
- 1000 convolution steps
- Select the fit with the best agreement (minimization of **$|1-x^2/NDF|$**)



I. Iterative approach

II. Fit Binning:

- ✓ Asymmetric fit limits:
  lower: $\mathbf{x_{min} - ((n-5)/10) \times \sigma}$
  upper: $\mathbf{x_{max} - ((n-5)/2) \times \sigma}$
  where 7 < n < 2 → **6 cases**
- ✓ Bin number defined at least as:
  $\mathbf{N_{bins} = \sqrt{N_{events}}}$
  augmented by:
  $\mathbf{(x_{max} - x_{min})/(0.5 \times \sigma \times \alpha/4)}$
  where 14 < α < 7 → **7 cases**

X

42 total iterations

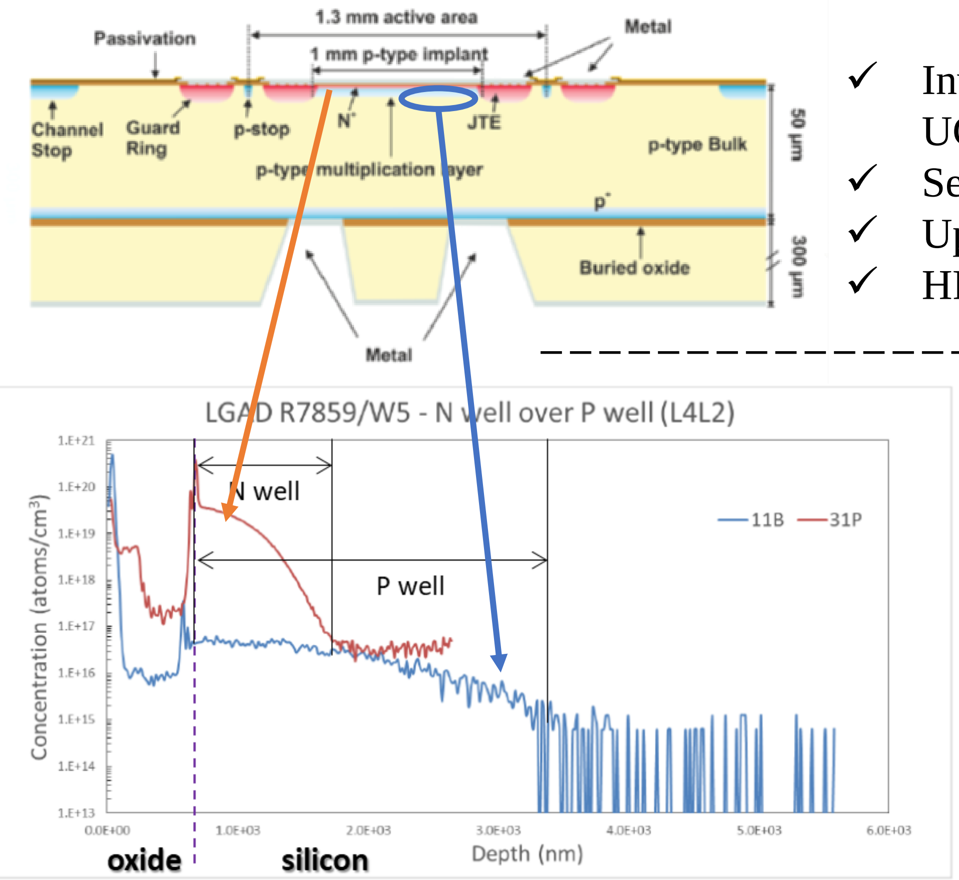
III. Parameter constraints:

- ✓ Asymmetric limits for Landau MVP:
  $\mathbf{x_{RMS} - 3\times\sigma < x_{RMS} < x_{RMS} + 3\times\sigma}$
- ✓ Function integral limits set to:
  $\mathbf{0.1\times Int. < X < 10\times Int.}$

IV. Initial values:

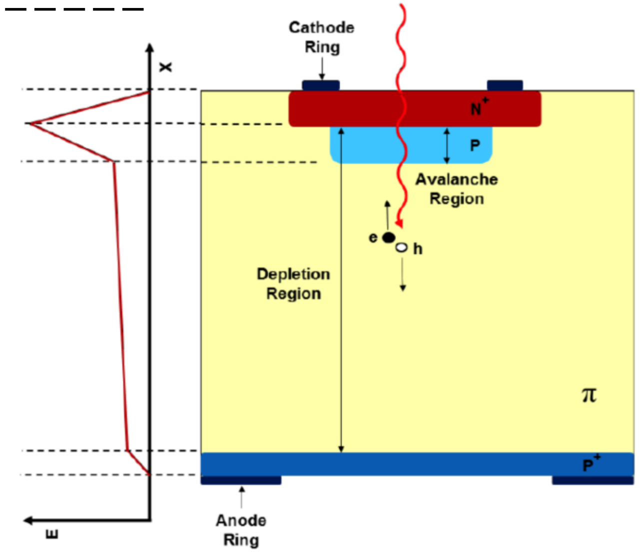
- ✓ Landau **MPV = $\mathbf{x_{RMS}}$**
- ✓ Convolution **Integral = distribution integral**
- ✓ Convoluted sigma set to : **σ / 4**

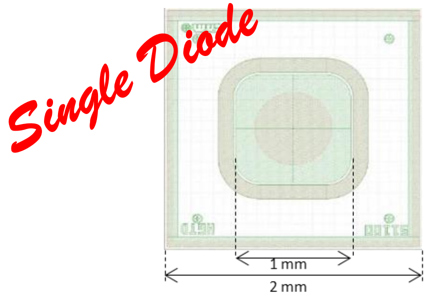
•LGAD Time Reference



- ✓ Invented at CNM, initially considered for tracking by IFAE, proposed for timing by UCSC
- ✓ Secondary p implant under collection electrode introducing moderate gain (10 -50)
- ✓ Up to 35 µm thickness on SoI or wafer to wafer bonding (typically 50 µm)
- ✓ HPK, CNM, FBK, MiCRON, BNL (USA), NDL (China)

- ✓ Requires precise diffusion control for layer thickness:
  - ✓ Thin highly doped n-well layer (~ 1 – 1.5 µm)
  - ✓ Gain layer ~ 2 µm
  - ✓ p-stop ~3 -3.5 µm
- ✓ Different gain layer species possible:
  - ✓ Boron (standard)
  - ✓ Gallium
  - ✓ Boron +Carbon





- ➢ 4” Si-on-Si wafers (High Resistivity ~2 kΩ•cm)
- ➢ 50 µm thickness on 250 µm support wafer
- ➢ Different implantation species
- ➢ Single diodes of active area 0.7 x 0.7 mm

Standard Boron
Boron + Carbon Spray (not confined)
Gallium